

FIG._2

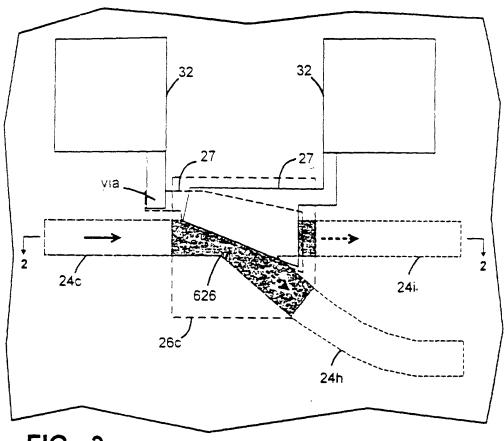


FIG._3

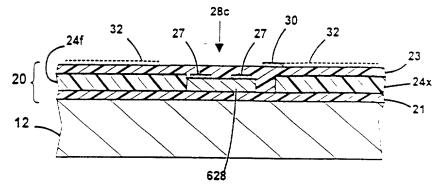


FIG._4-1

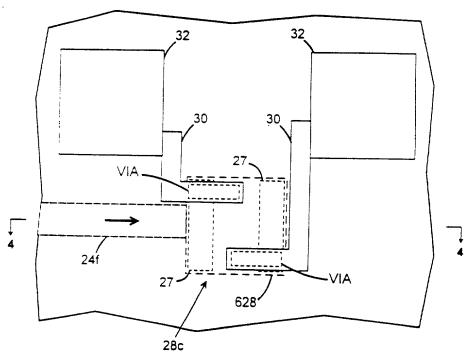
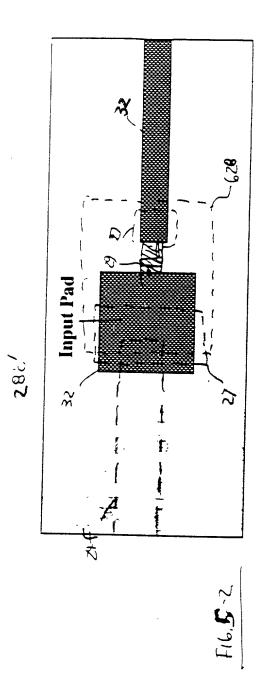
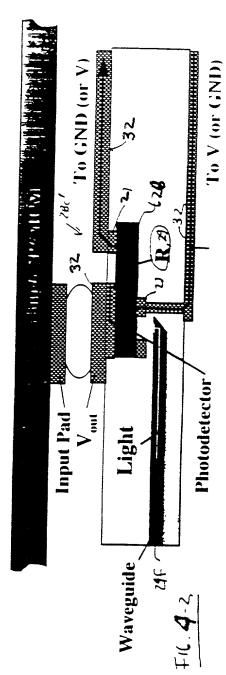
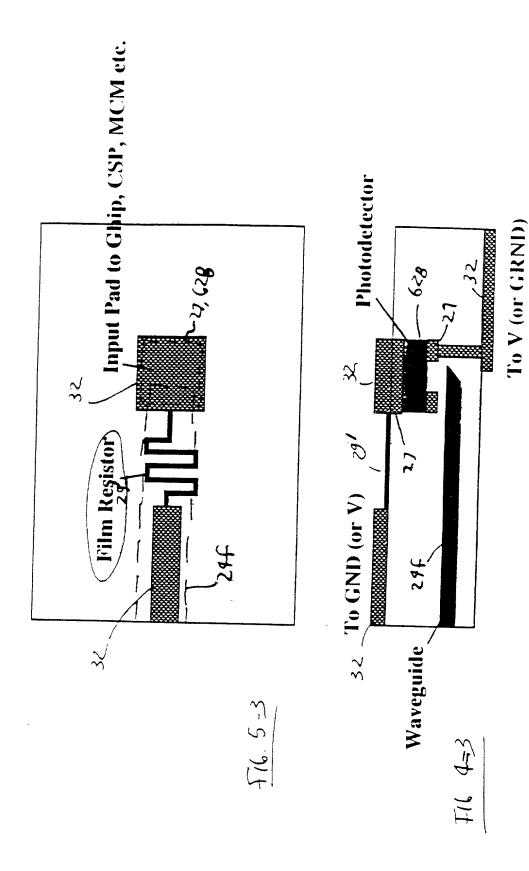
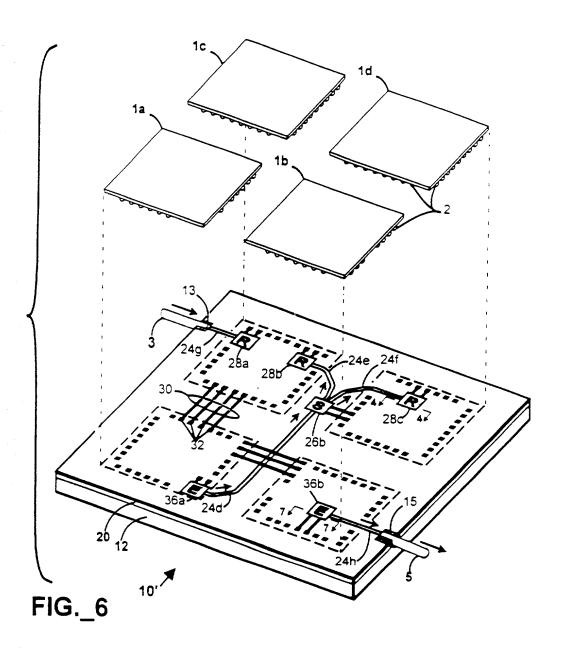


FIG._5-1









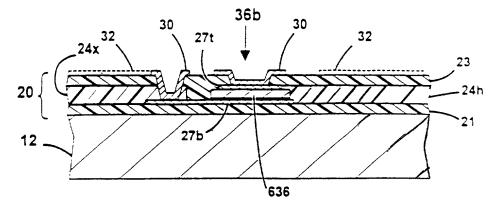
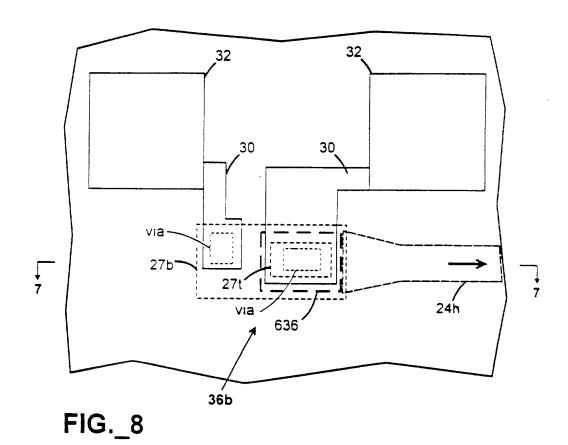
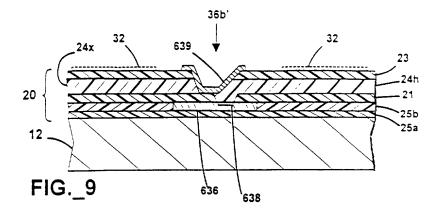


FIG._7





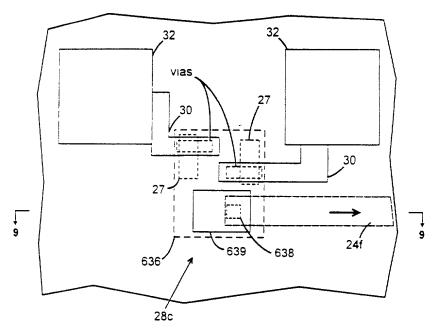
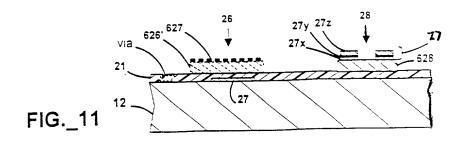
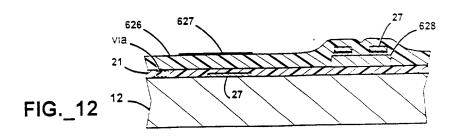
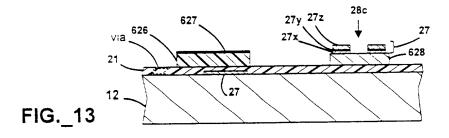
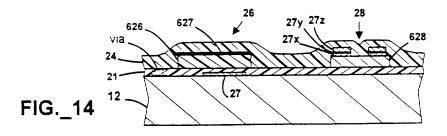


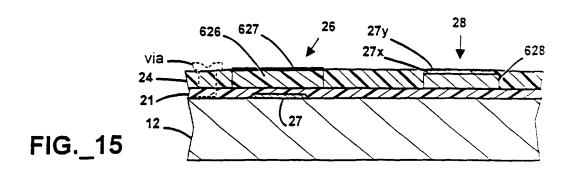
FIG._10

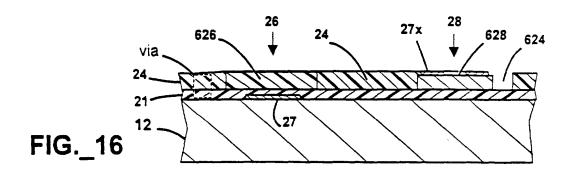


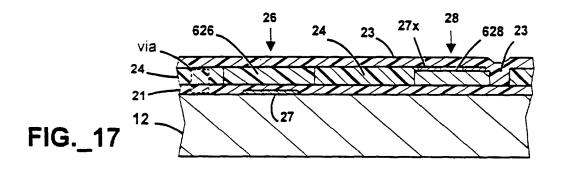


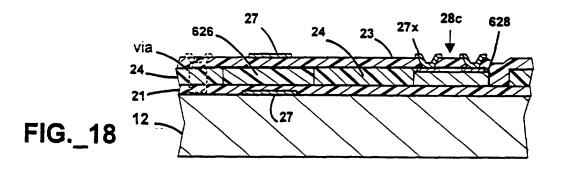












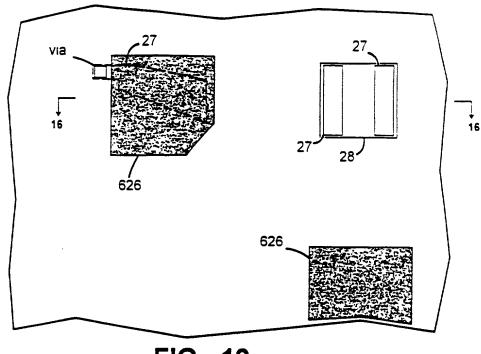


FIG._19

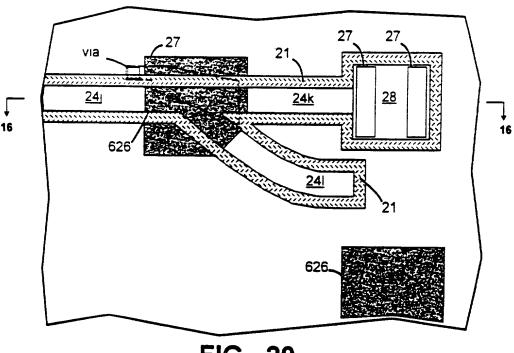
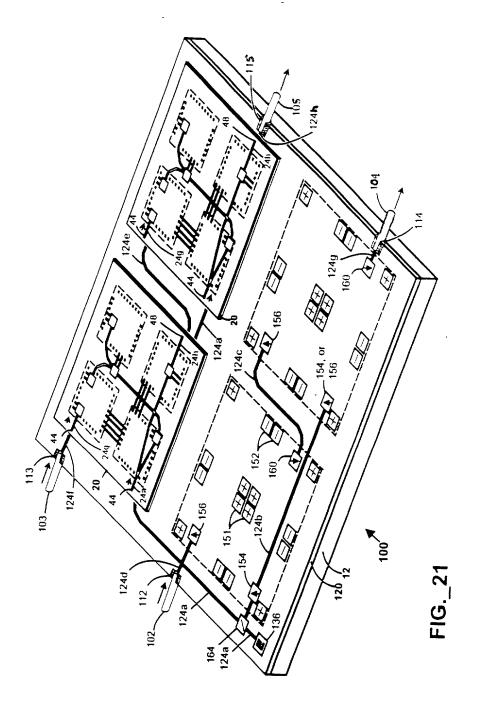


FIG._20



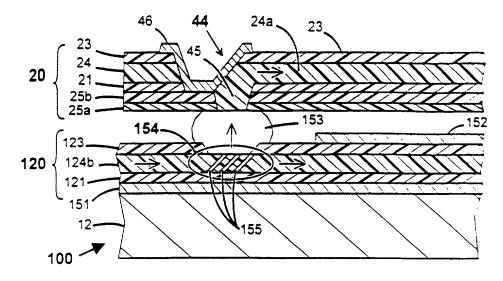


FIG._22

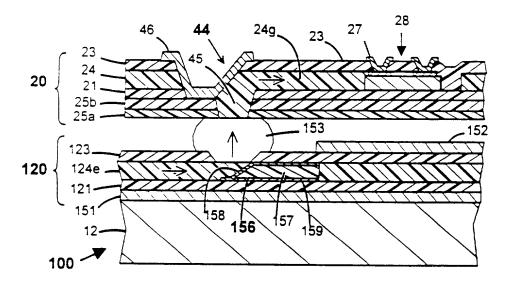


FIG._23

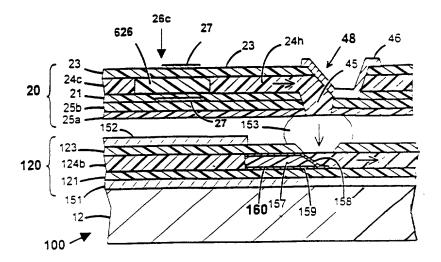
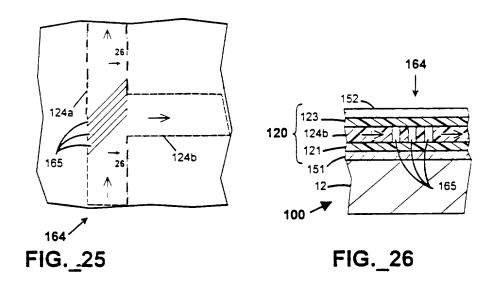
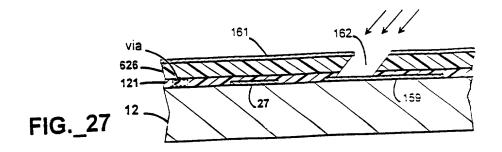
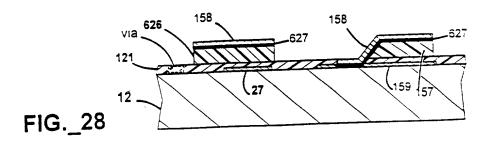
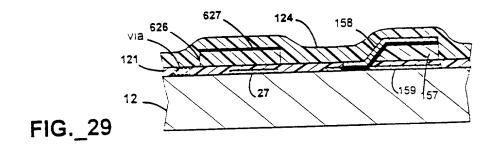


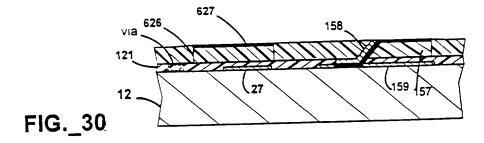
FIG._24

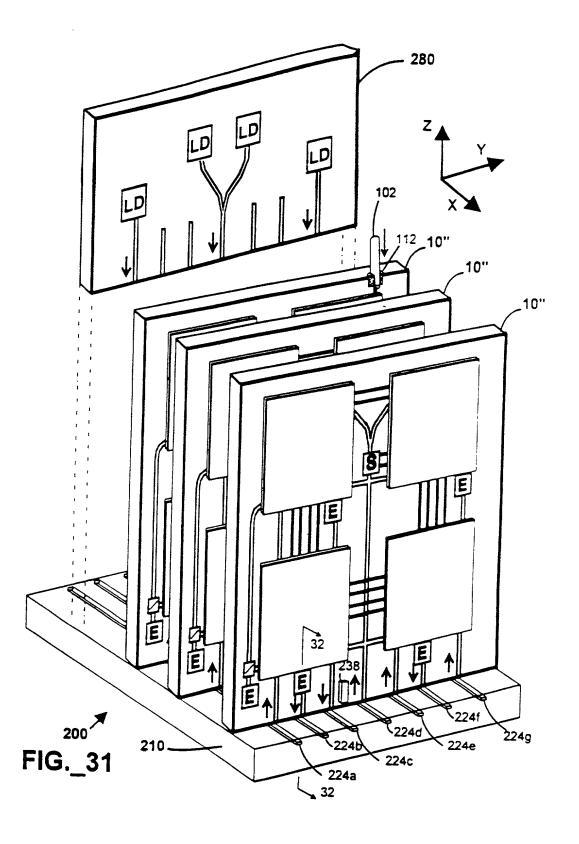


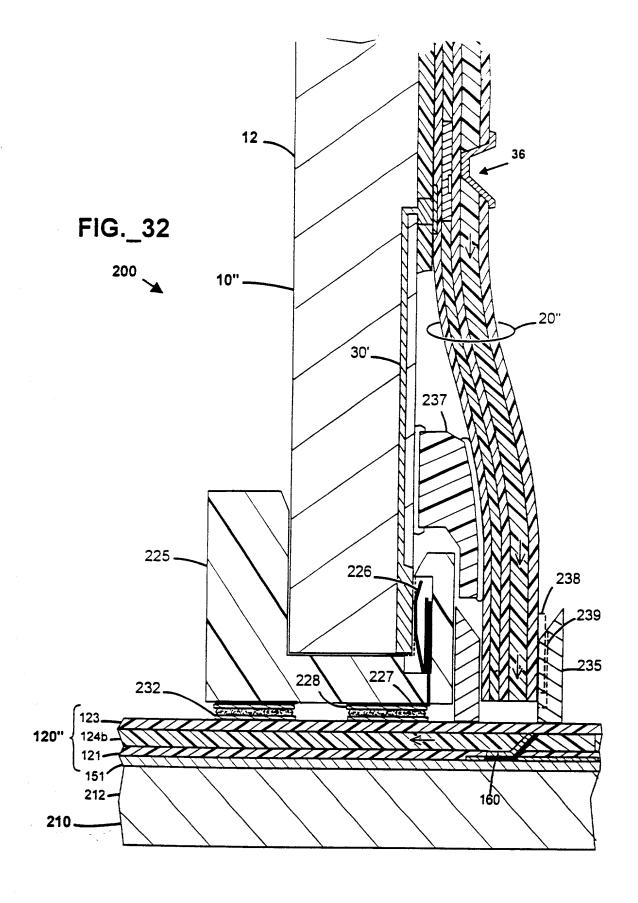


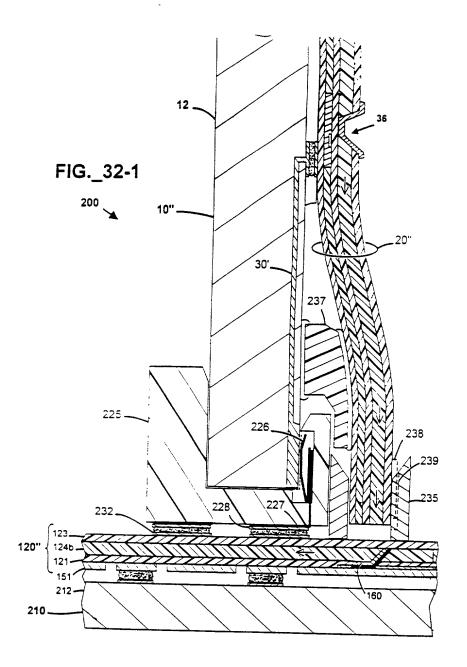


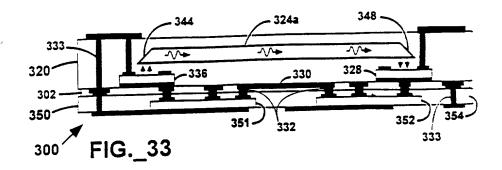


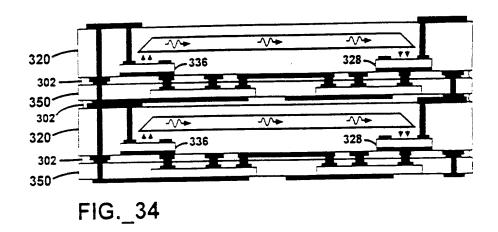


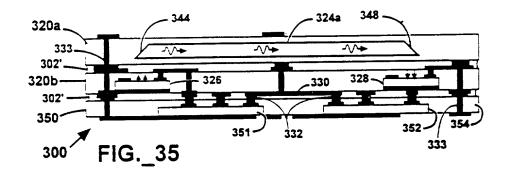












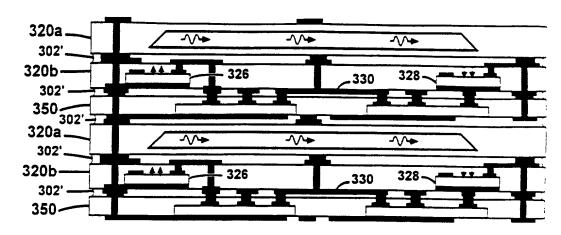
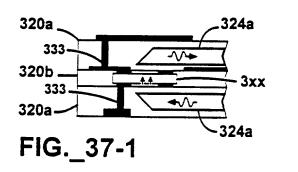
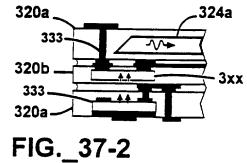
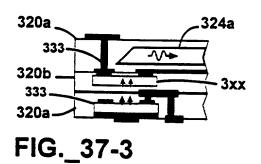


FIG._36







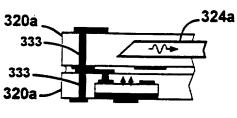


FIG._37-4

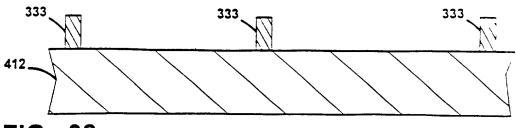


FIG._38

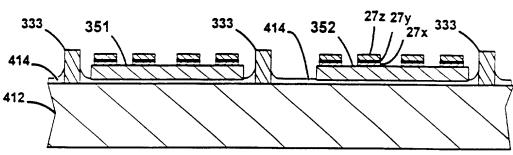


FIG._39

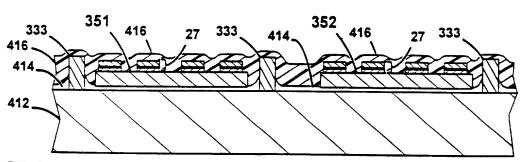


FIG._40

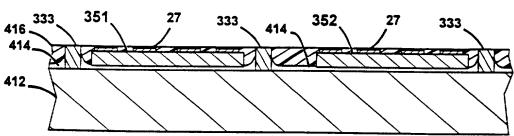


FIG._41

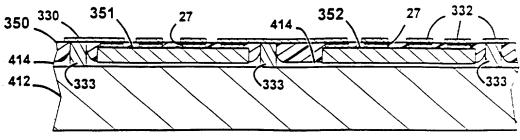


FIG._42

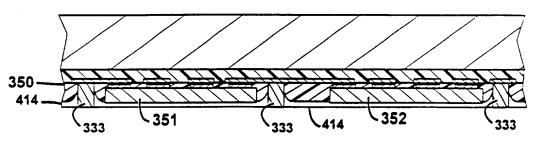


FIG._43

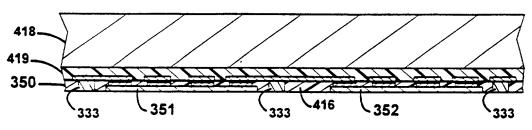


FIG._44

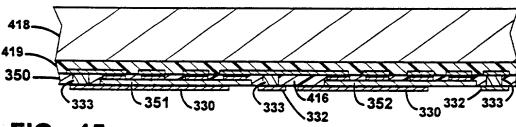
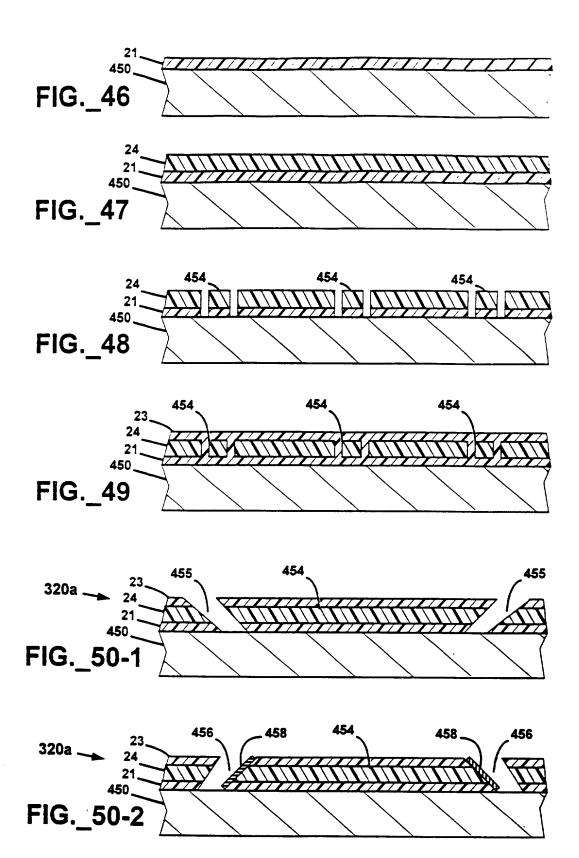
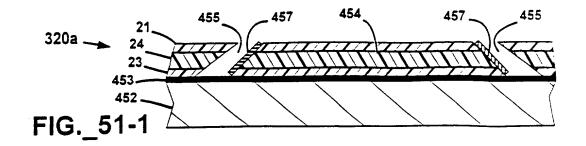
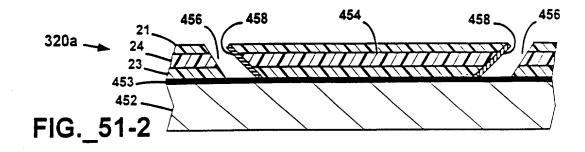
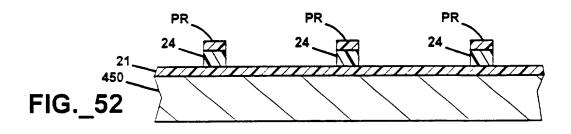


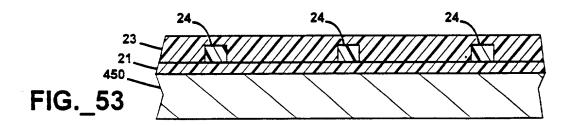
FIG._45

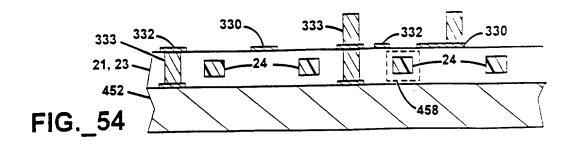


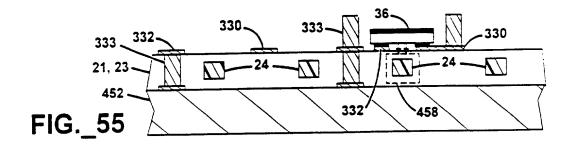


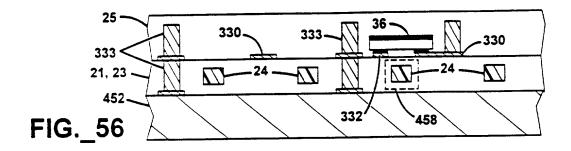


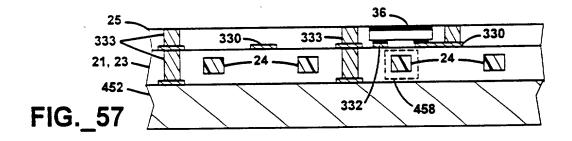


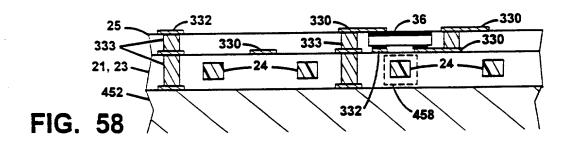


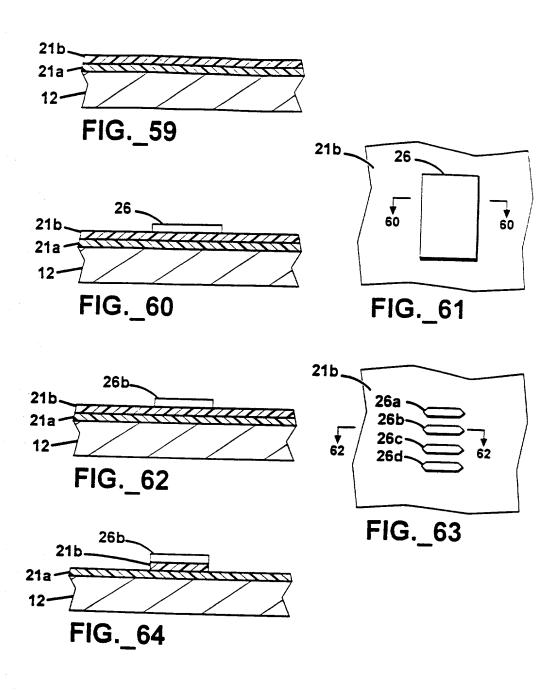


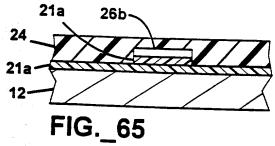


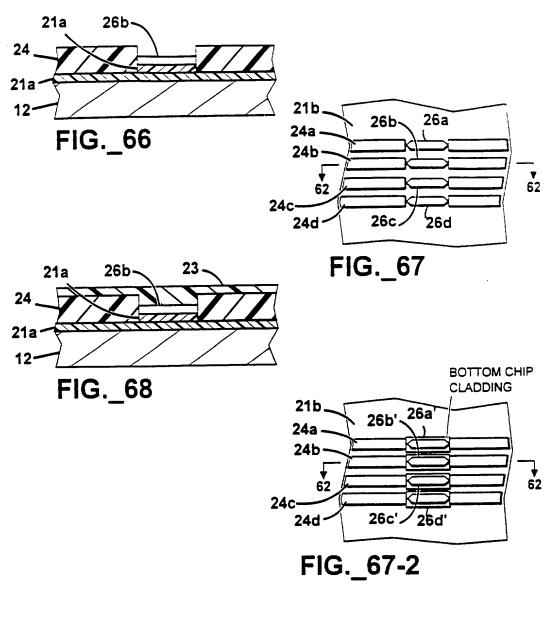


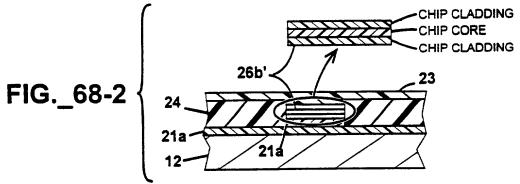


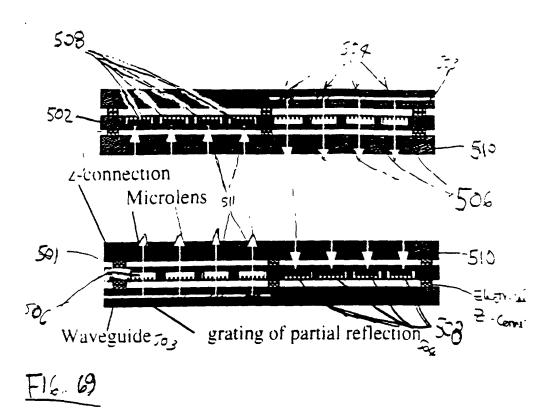


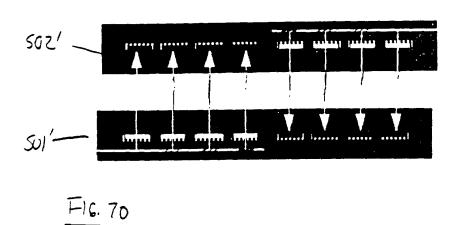


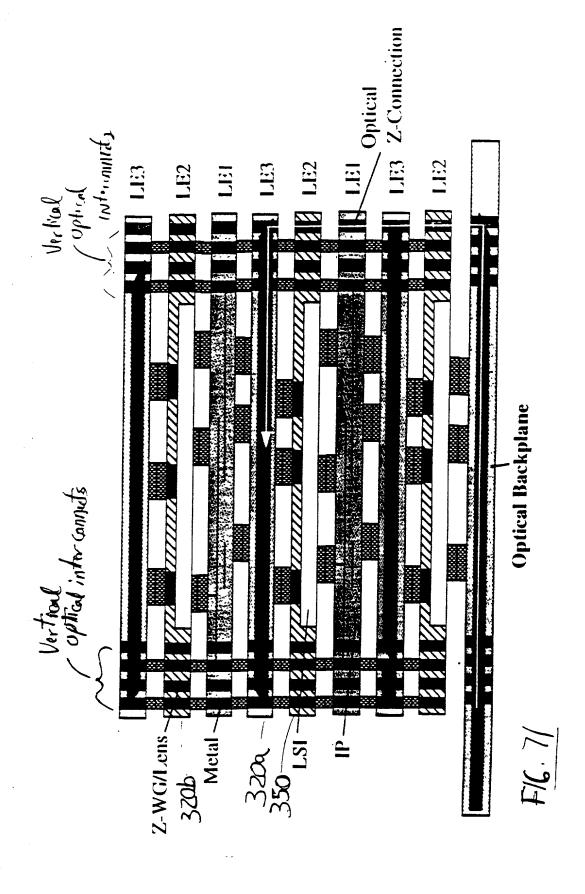


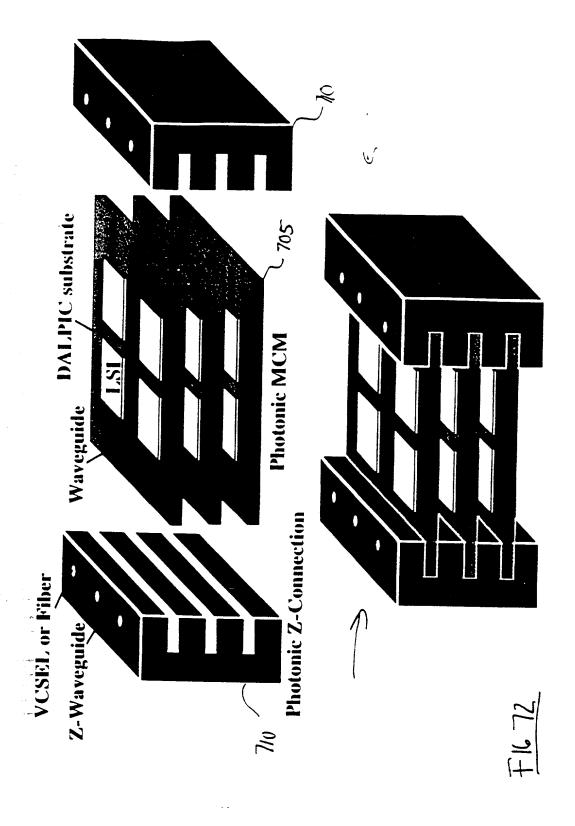


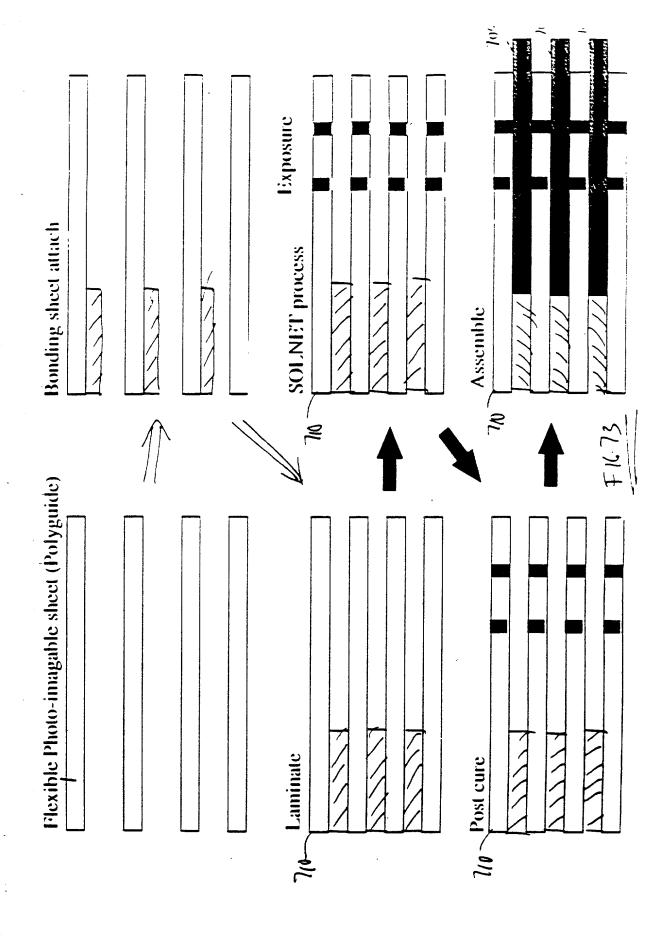












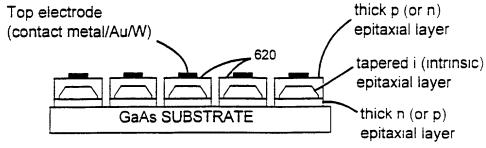
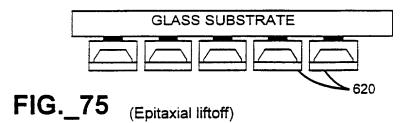


FIG._74 (Epitaxial growth and patterning)



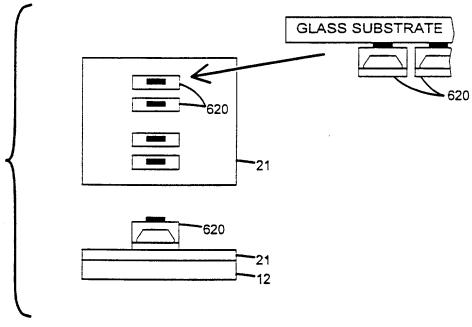
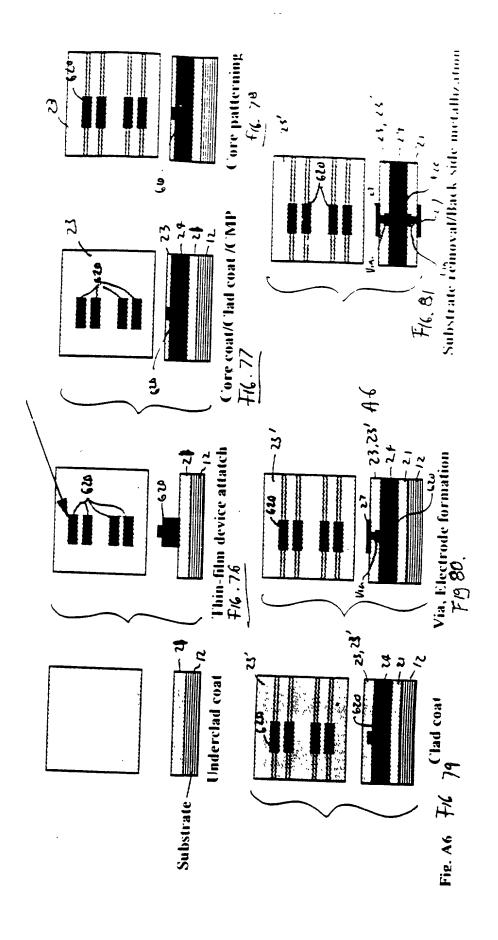
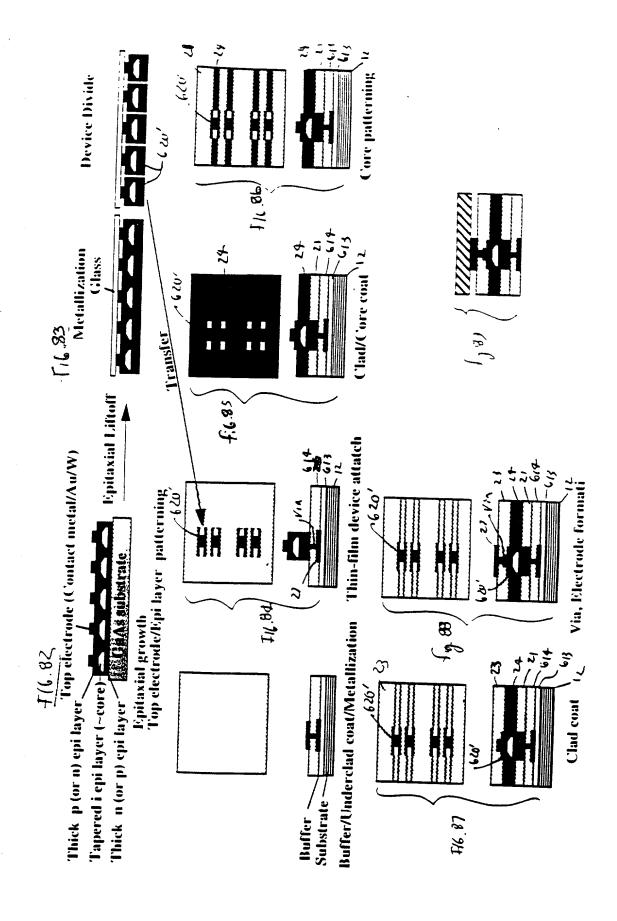
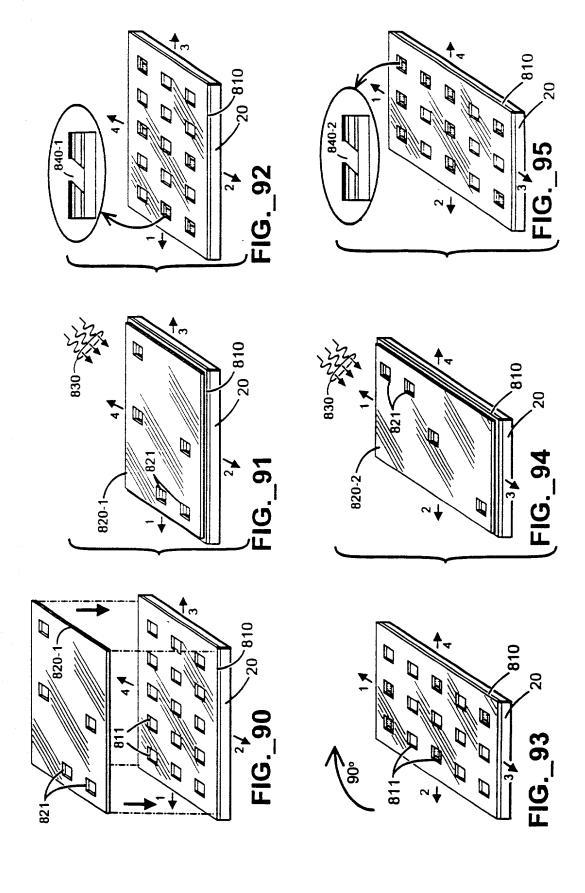
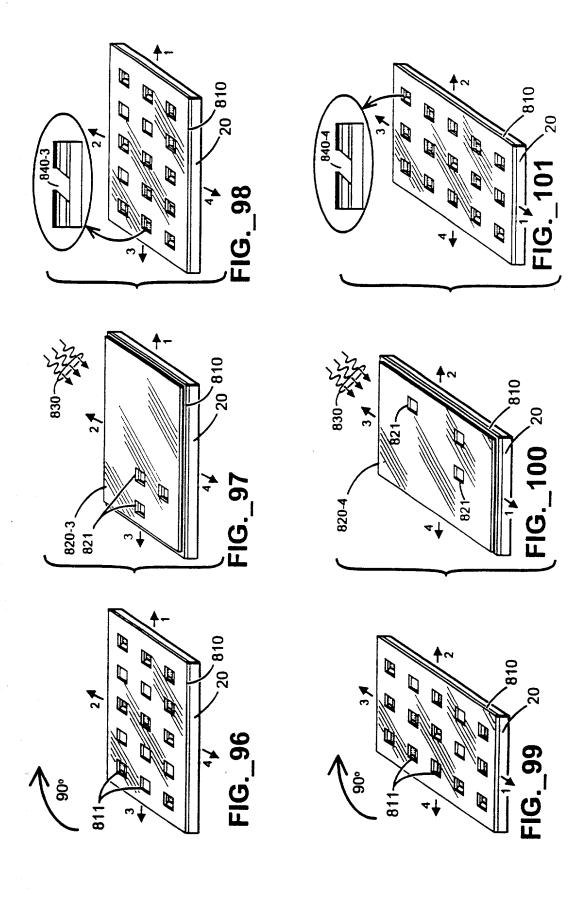


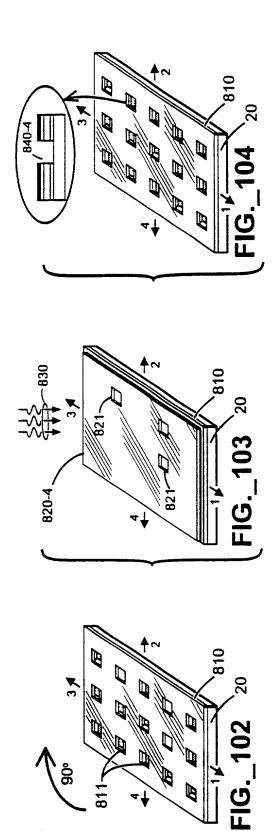
FIG._76 (Transfer)

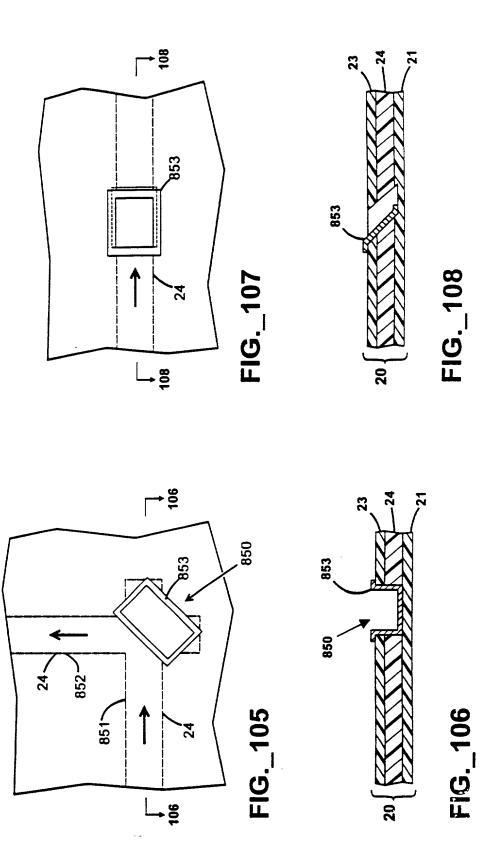






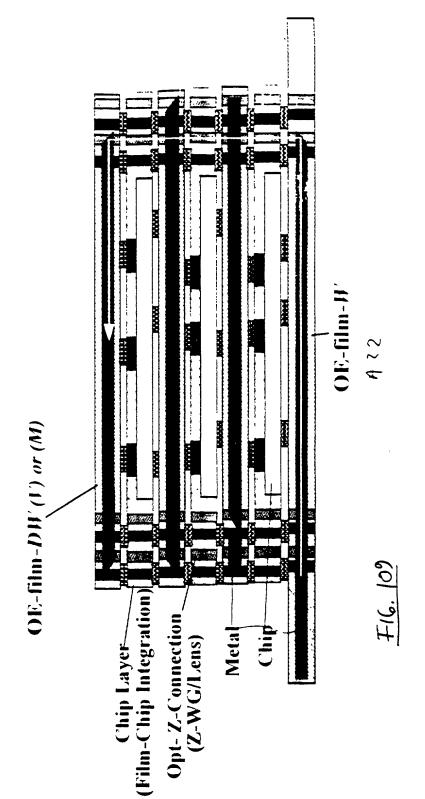




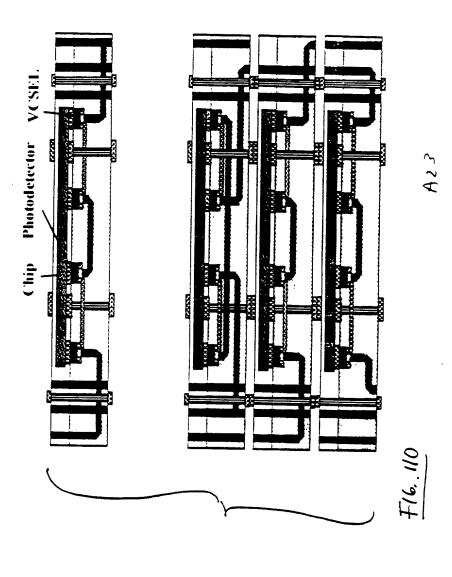


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GS CX/CXX OE Solution --- OE-3D-Stack

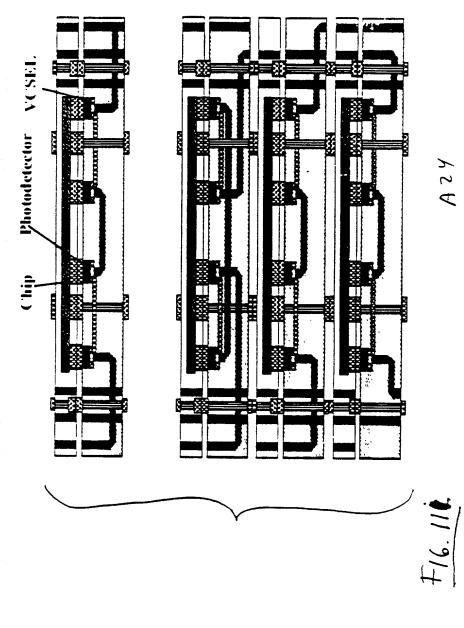


2/23/99-added 7



(2/23/99) AA1 Detail picture Example for 3D-stack?

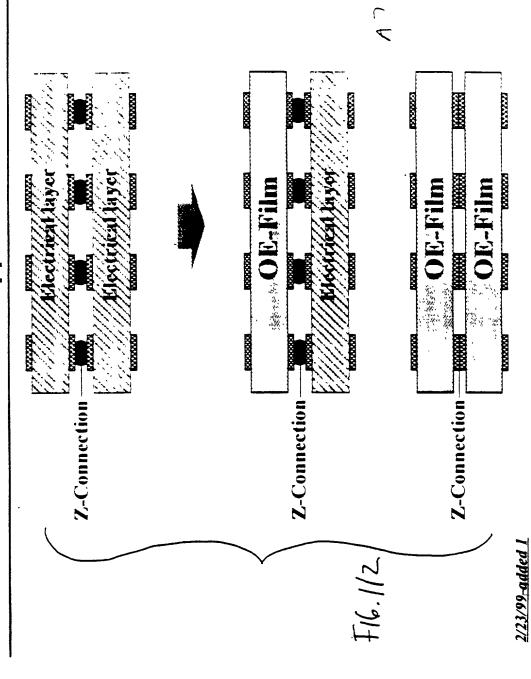
(New version of the AAL of 2/5/99)



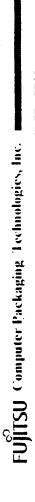
(2/23/99) AA2 Detail picture Example for 3D-stack?

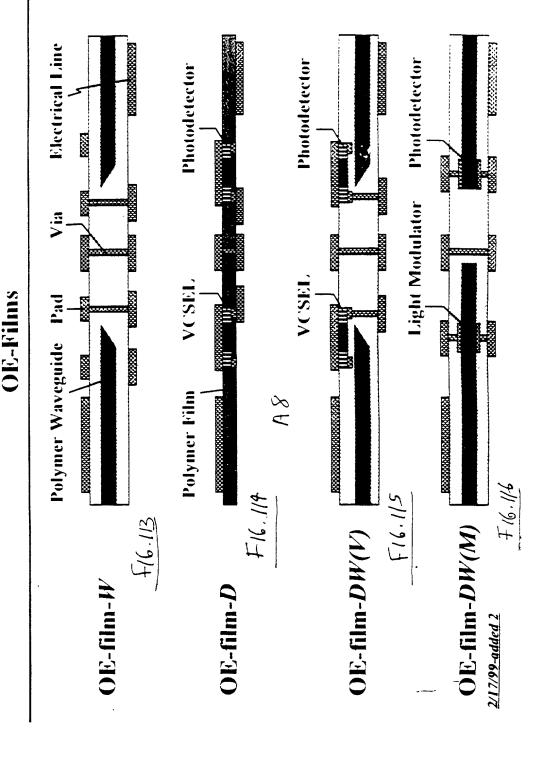
(New version of the AA2 of 2/5/99)

Film/Z-Connection Application to OE-Substrate

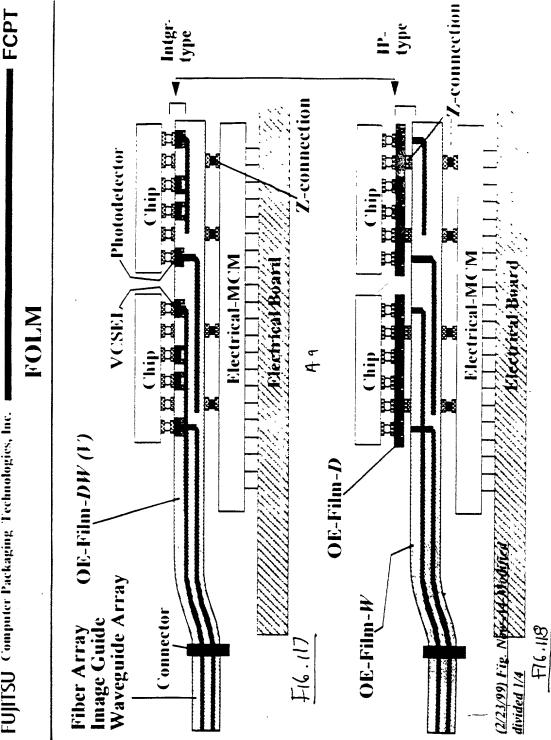


A4 12





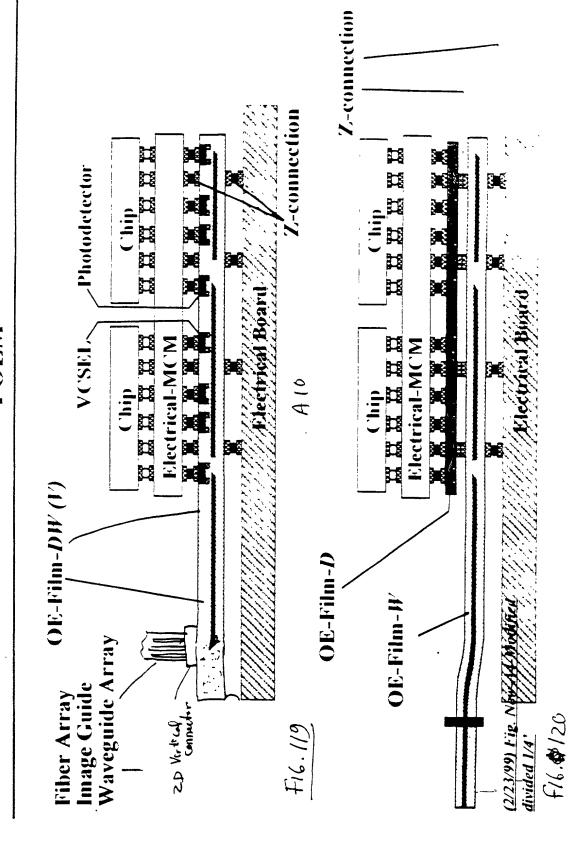
FUJITSU Computer Packaging Technologies, Inc.



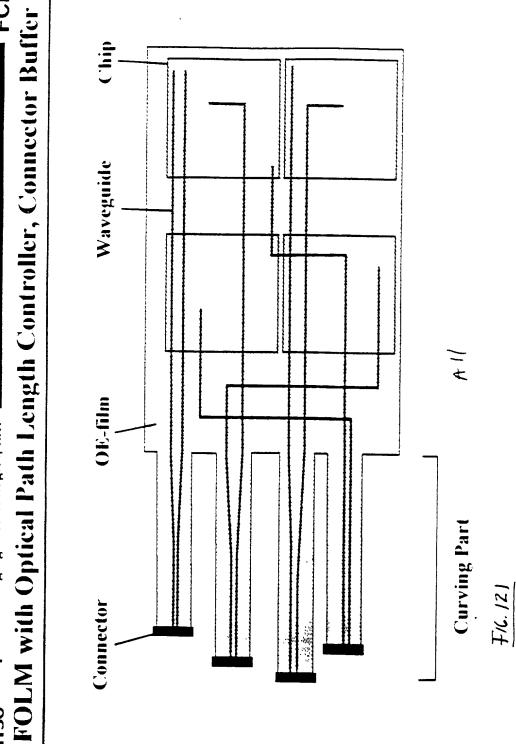
FCPT

FUITSU Computer Packaging Technologies, Inc.

FOLM

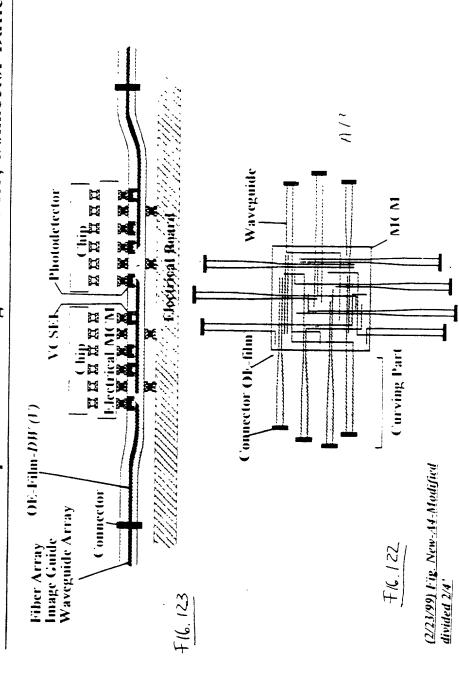


FUNTSU Computer Packaging Technologies, Inc.



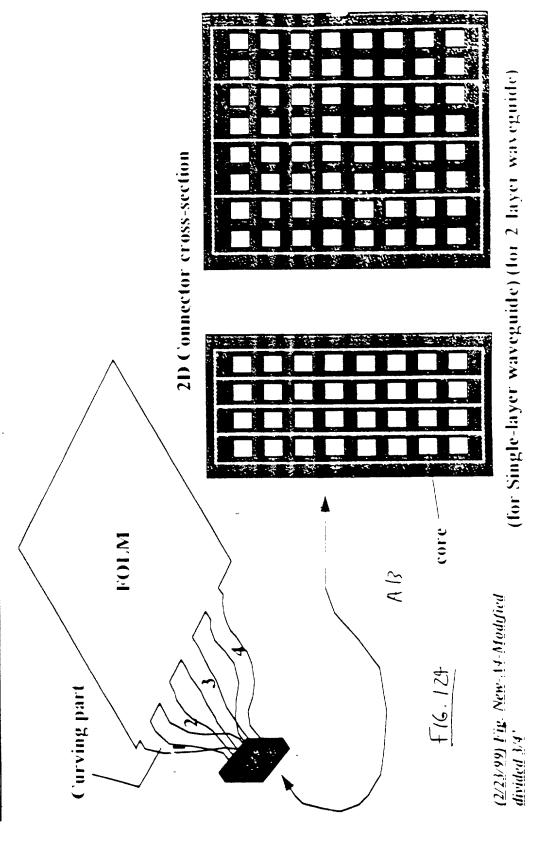
(2/17/99) Fig. New-A4-Modified divided 2/4

· FCPT FOLM with Optical Path Length Controller, Connector Buffer FUJITSU Computer Packaging Technologies, Inc. 1



FUJITSU Computer Packaging Technologies, Inc.

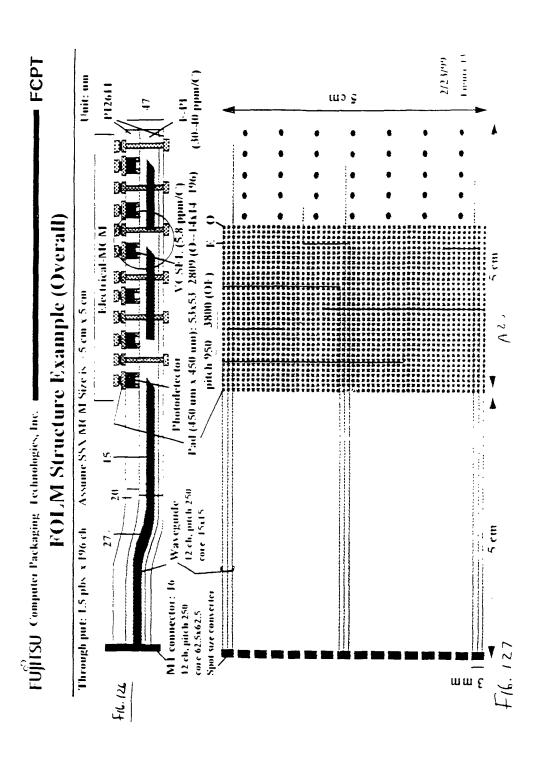
FOLM with 2D Waveguide Connector



FUJITSU Computer Packaging Technologies, Inc.

External Light Light Modulator Z-Connection FOLM: High-Speed Option Chip (MCM, CSP) OE-film-DH(M) Photodetector Array Waveguide Fiber Ribbon Image guide Connector

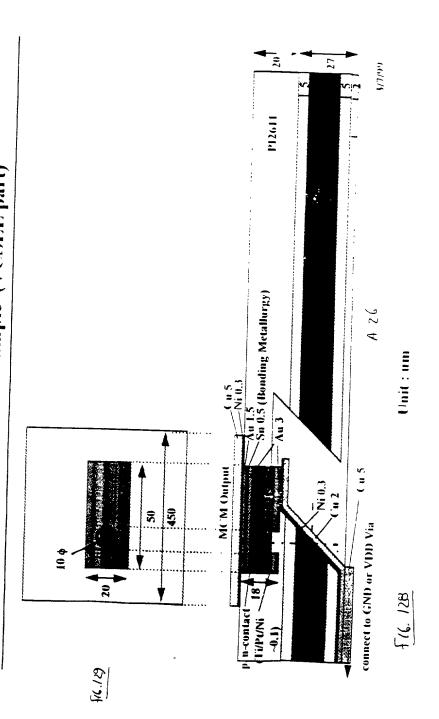
(2/12/99) f. 1g. New-A4-Modified divided 4/4



TUMESU Computer Packaging Technologies, Inc.

FOLM Structure Example (VCSEL part)

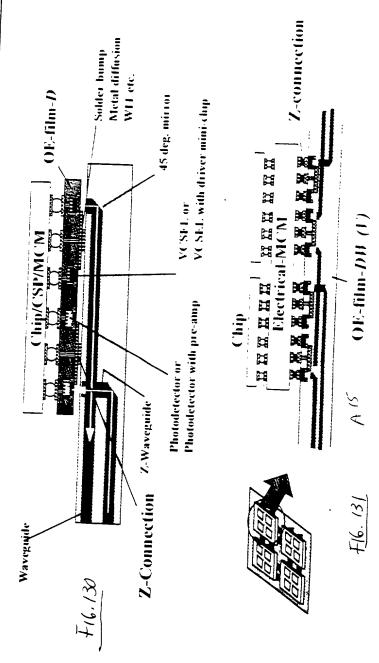
FCPT



FUJITSU Computer Packaging Technologies, Inc.

OE-film: OE-IP, OE-Film-MCM

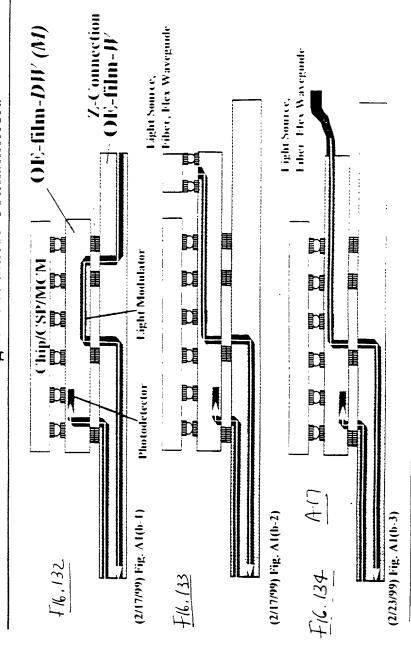
• FCPT



(2/23/99) Fig. New-A1-Modified

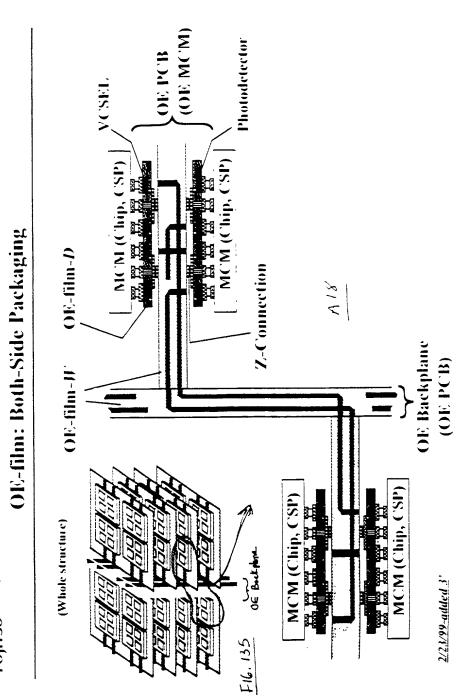
FUJISU Computer Packaging Technologies, Inc.

OE-film: Light Modulator Transmitters



Examples of Light Modulators: Electro Optic (FO) Modulator, Hectro Absorption (UA) Modulator

FUJITSU Computer Packaging Technologies, Inc.



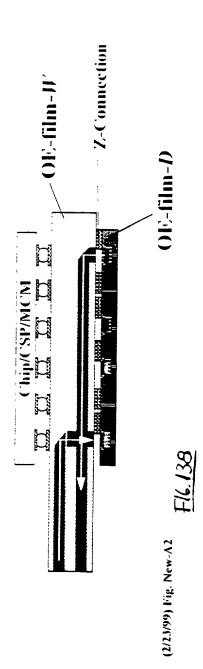
FUJISU Computer Packaging Technologies, Inc.

Line length conti Z.Connection Z-Connection Photodiode Film Waveguide with Device Integration l ight Madulator \IBS.)\ Control of the Contro Direct Jump from LSI IN HAVIS I Photodetector D Fiber Ribbon Connector Fig. New-A4-Modified F16.136

Computer Packaging Technologies, Inc.

■ FCPT

OE IP is Placed on the Oposit Side



N 20

FUJIISU Computer Packaging Technologies, Inc.

OE MCM

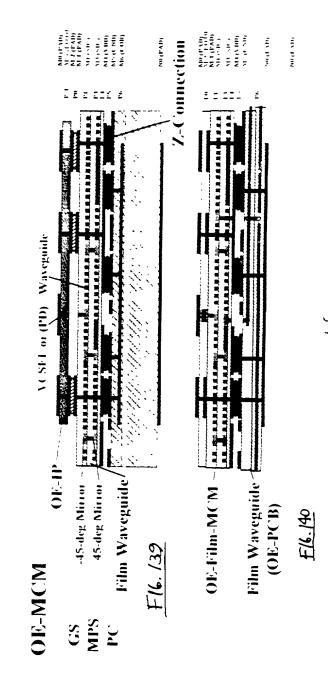


Fig. A5-Modified

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OE-film: Smart Pixel

FCPT

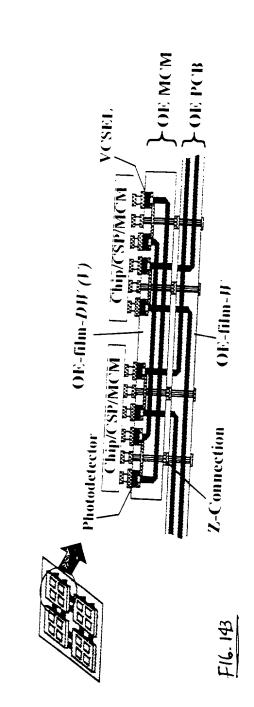
Chip/CSP/MCM
OE-film-D

F16 141



2/23/99-udded 6

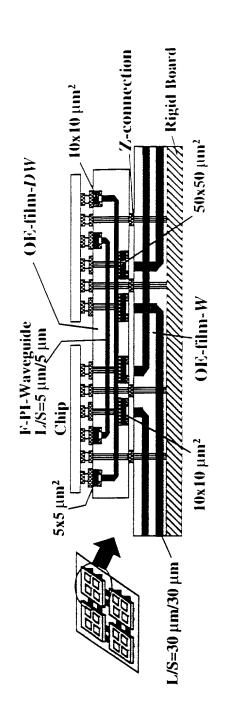
OE-Film/OE-Film Stack --- Back-Side Connection



911

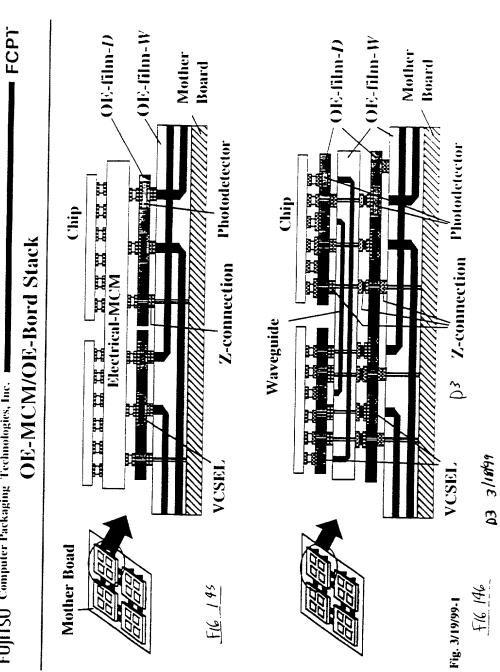
2/23/99-udded 4"

OE-Film/OE-Film Stack --- Back-Side Connection FUJITSU Computer Packaging Technologies, Inc.



F16 144

FUJTSU Computer Packaging Technologies, Inc.



FUJIISU Computer Packaging Technologies, Inc.

Doviese Integration Desses

the state of the state of the 182 Roman Roman Fil. 148 Device Integration Process OE-film-D → (6) Jump to the waveguide formation process (5) Vias/Pads/Lines formation (1) Pads/Lines formation (2) Placement of Thin film devices ¬▼ (6) Substrate removal (4) Planarization (3) Polymer coaf

OE-film DH(I)

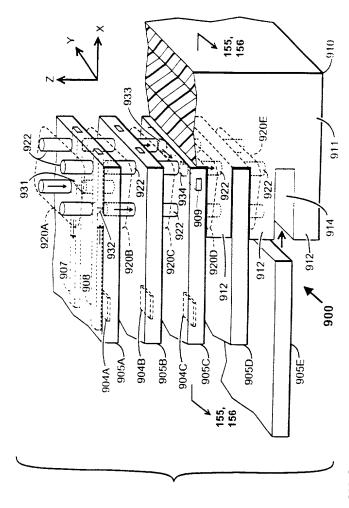
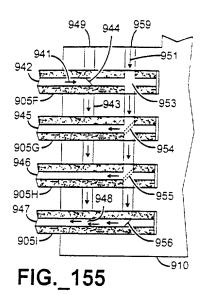


FIG._154



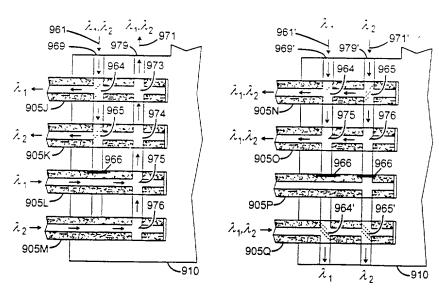
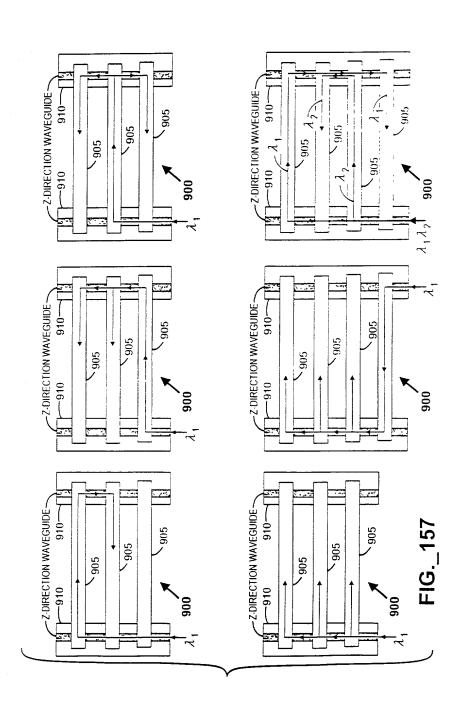
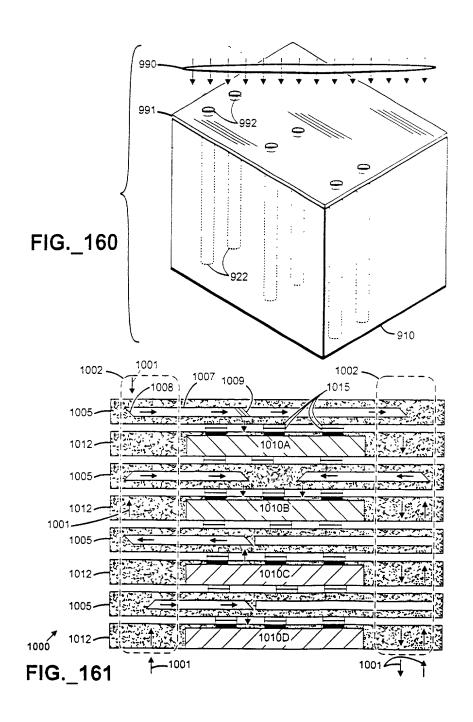
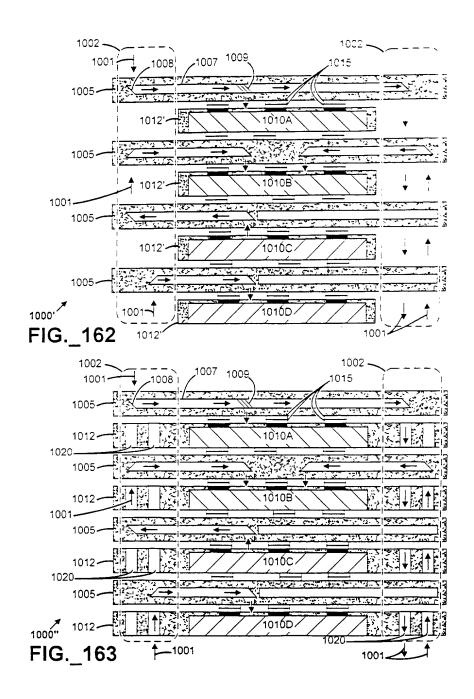


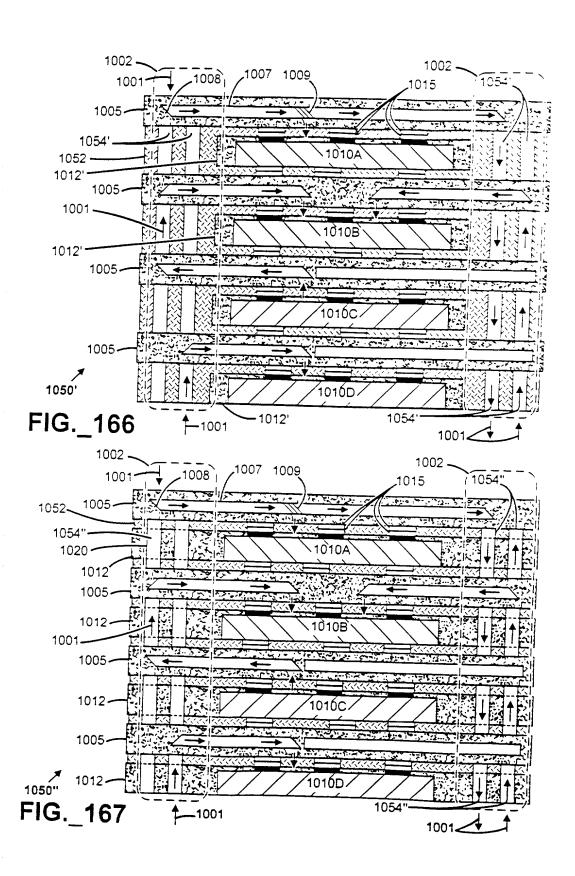
FIG._156-1

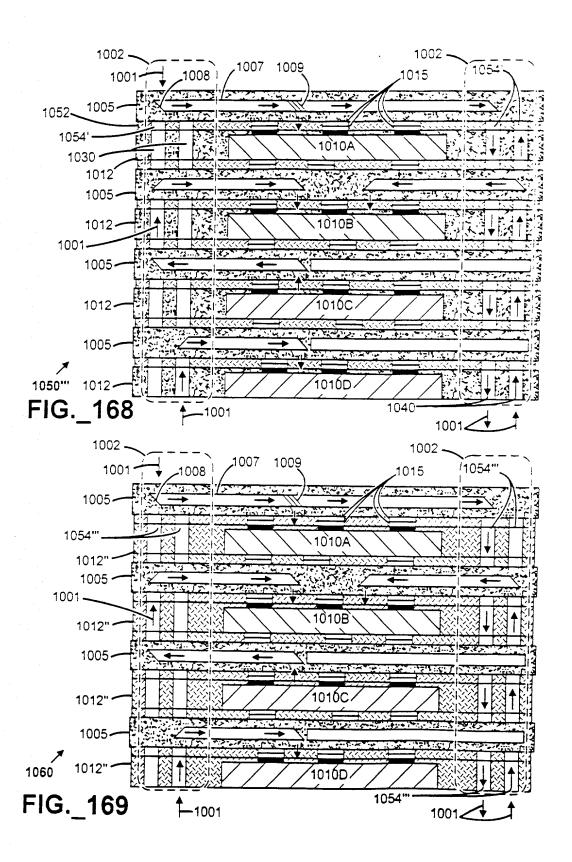
FIG._156-2











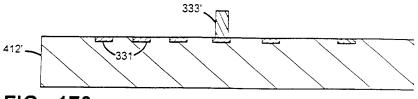


FIG._170

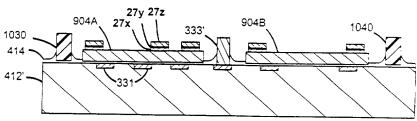


FIG._171

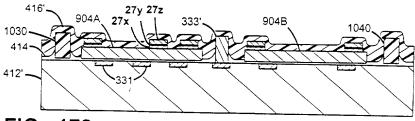


FIG._172

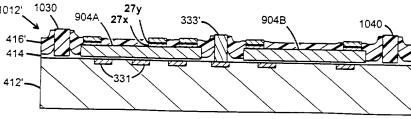
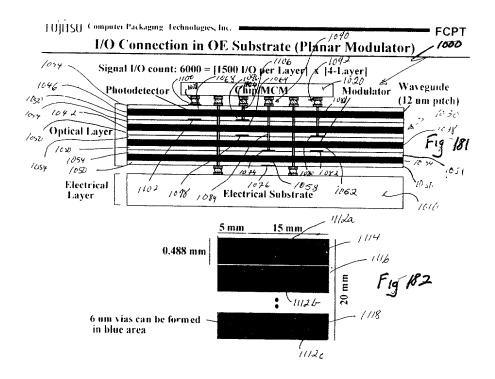
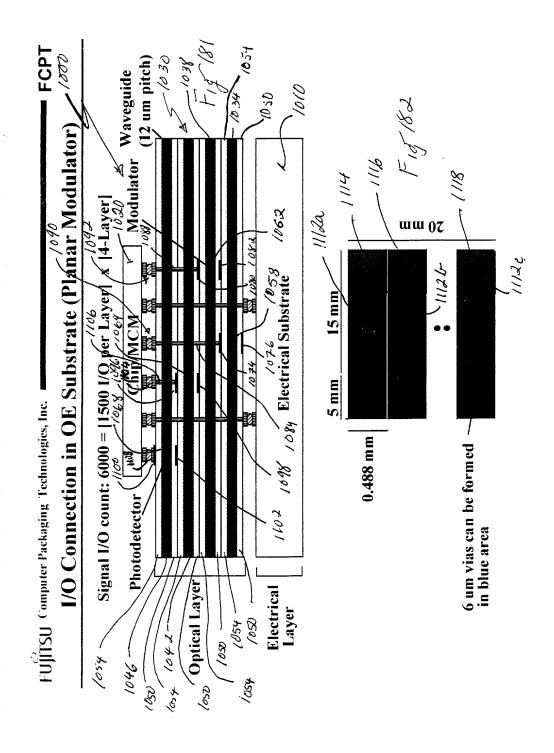
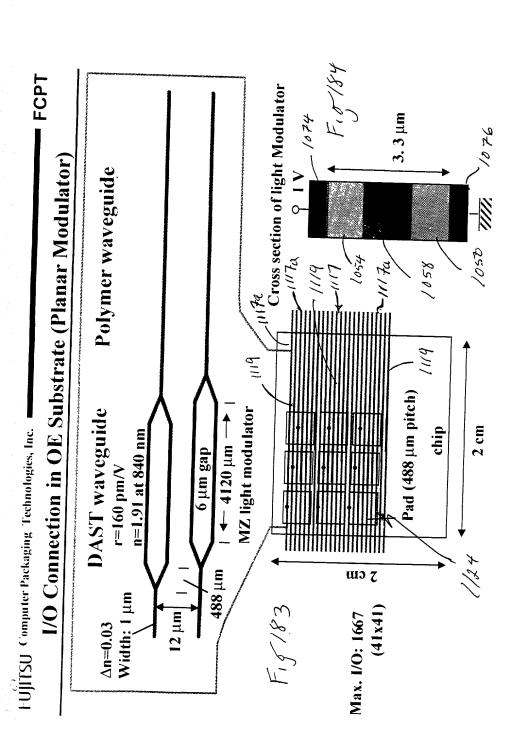


FIG._173

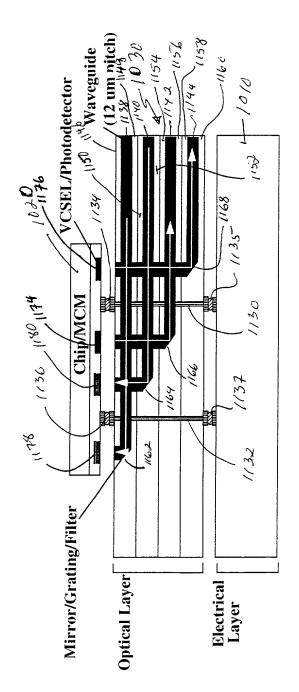






I/O Connection in OE Substrate (OE-VLSI) EUJTSU Computer Packaging Technologies, Inc.

Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer]

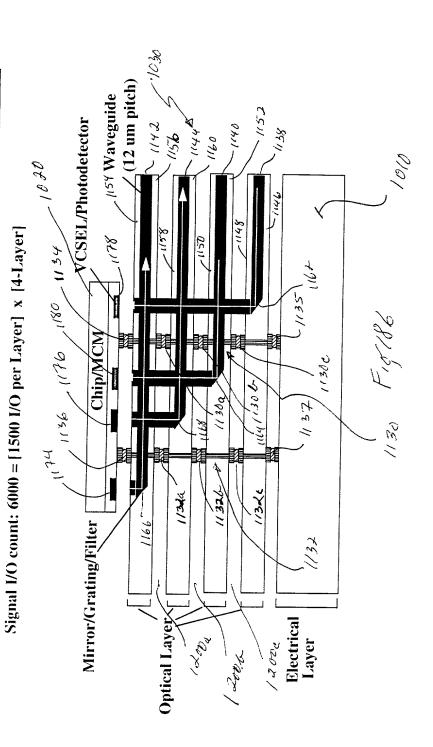


F19 185

FUJITSU Computer Packaging Technologies, Inc. 1

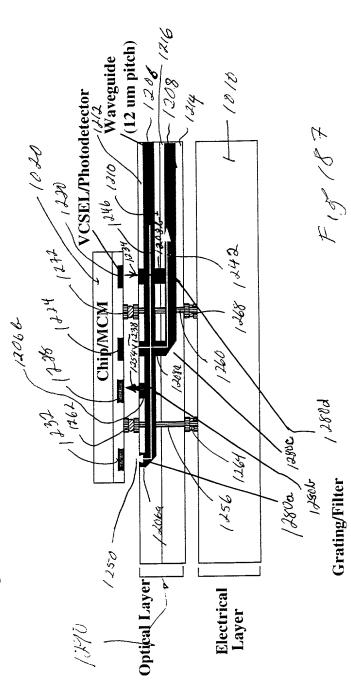
FCPT

I/O Connection in OE Substrate (OE-VLSI)



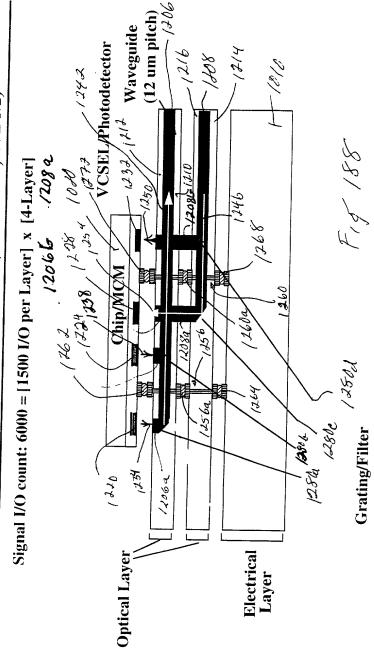
I/O Connection in OE Substrate (OE-VLSI, WDM) FUJITSU Computer Packaging Technologies, Inc.

Signal I/O count: $6000 = [1500 \text{ I/O per Layer}] \times [4-\text{Layer}]$



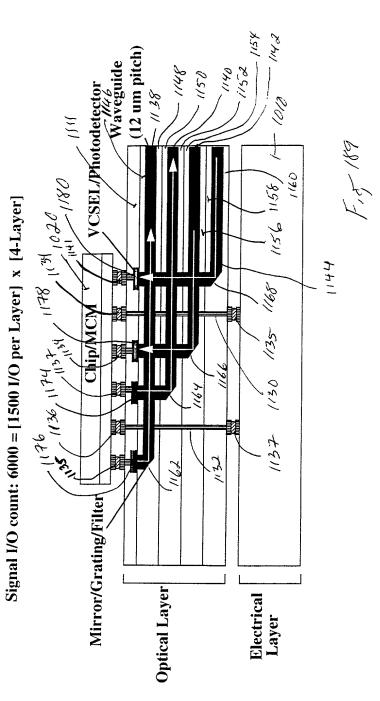
FUJITSU Computer Packaging Technologies, Inc.

I/O Connection in OE Substrate (OE-VLSI, WDM)



FUMTSU Computer Packaging Technologies, Inc.

I/O Connection in OE Substrate (Active OE Layer)



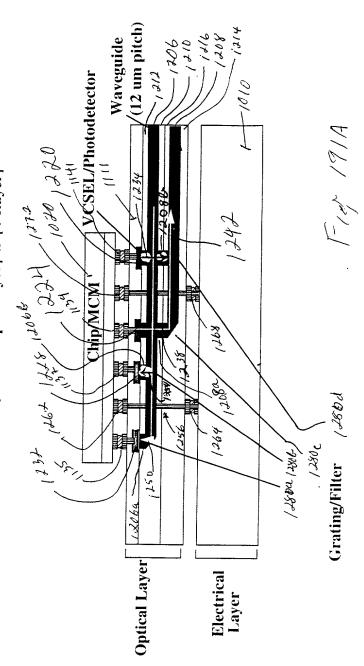
FUJTSU Computer Packaging Technologies, Inc.

VO Connection in OE Substrate (Active OE Layer)

Waveguide (12 um pitch) VCSEL/Photodetector 0.511 4411 ~ 1142 -1156 1136 1180 4 1176 1151 3211 1136 1137 1130 1176 1151 Signal I/O count: 6000 = [1500 I/O per Layer] x [4-Layer] Chip/MCM 0811 Mirror/Grating/Filter Optical Layer-Electrical Layer

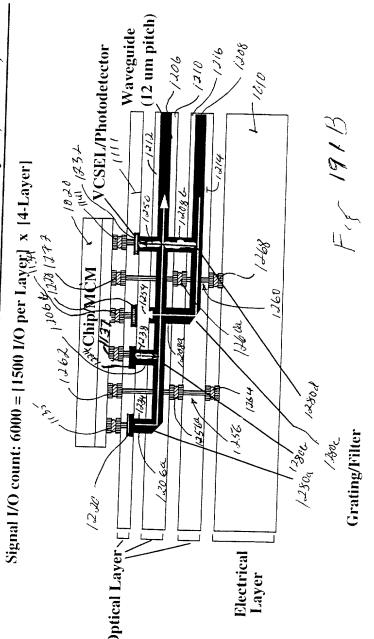
I/O Connection in OE Substrate (Active OE Layer, WDM) FUJITSU Computer Packaging Technologies, Inc.

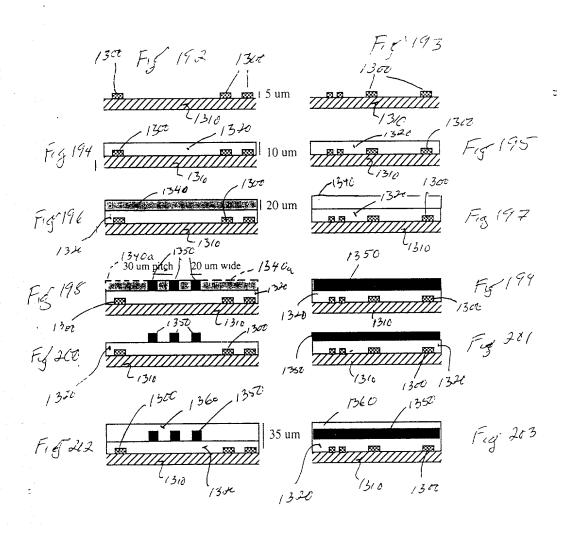
Signal I/O count: $6000 = [1500 \text{ I/O per Layer}] \times [4-\text{Layer}]$

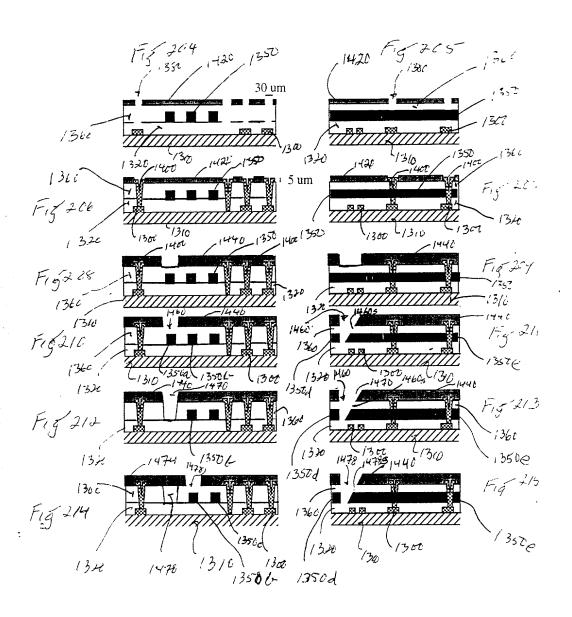


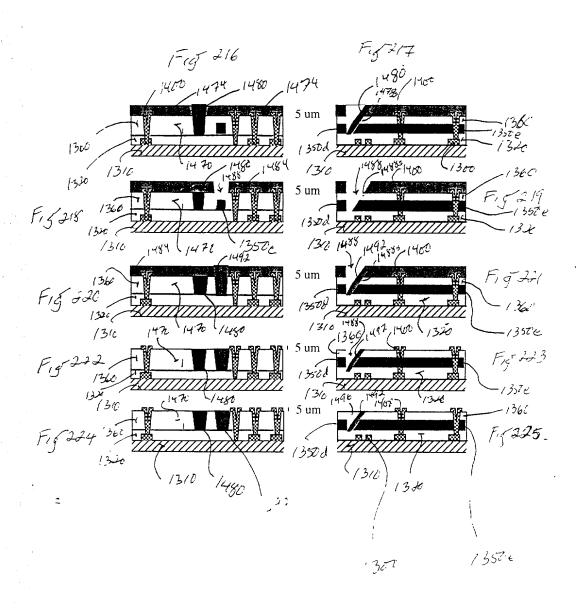
FUITSU Computer Packaging Technologies, Inc.

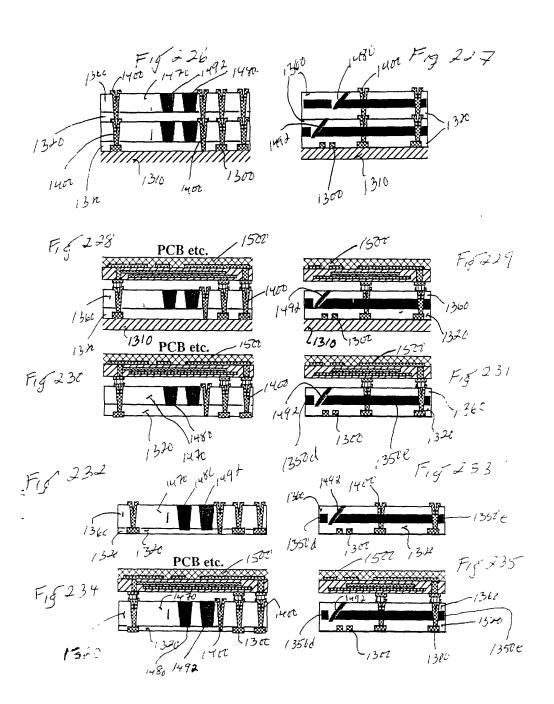
I/O Connection in OE Substrate (Active OE Layer, WDM)

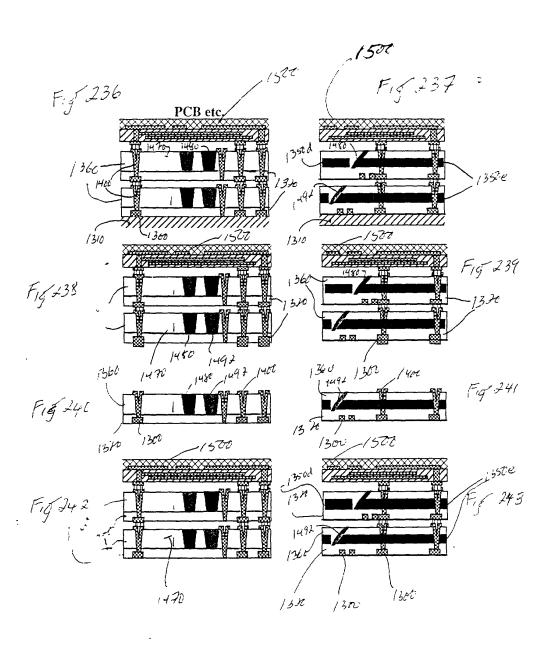


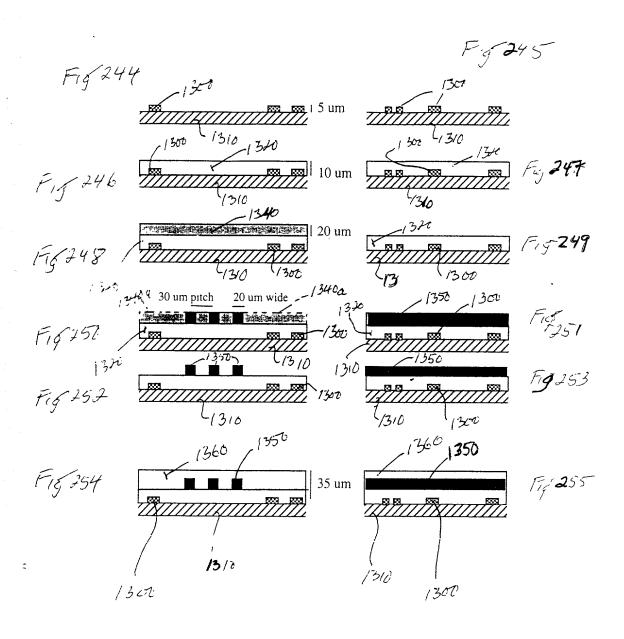


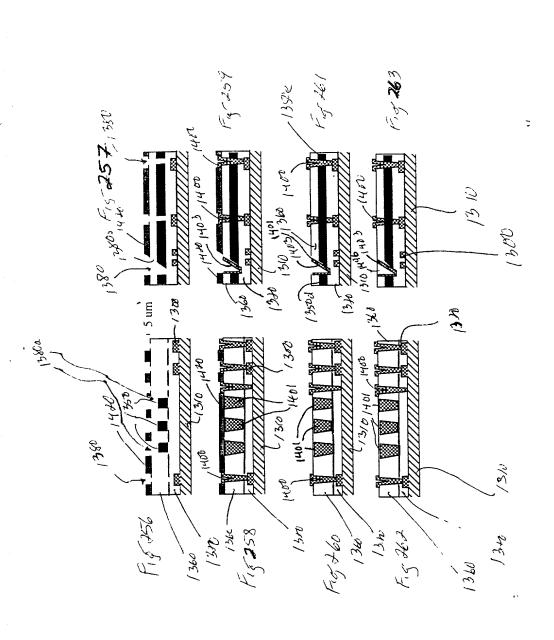


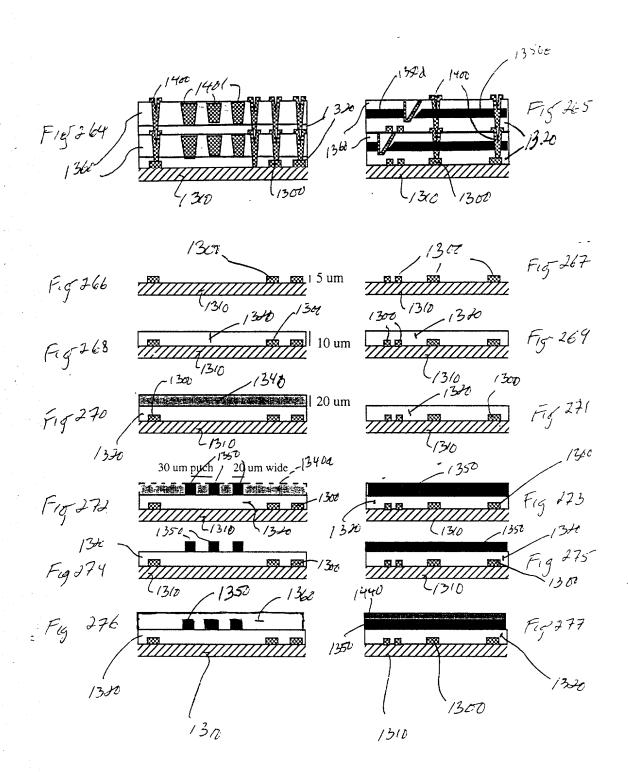


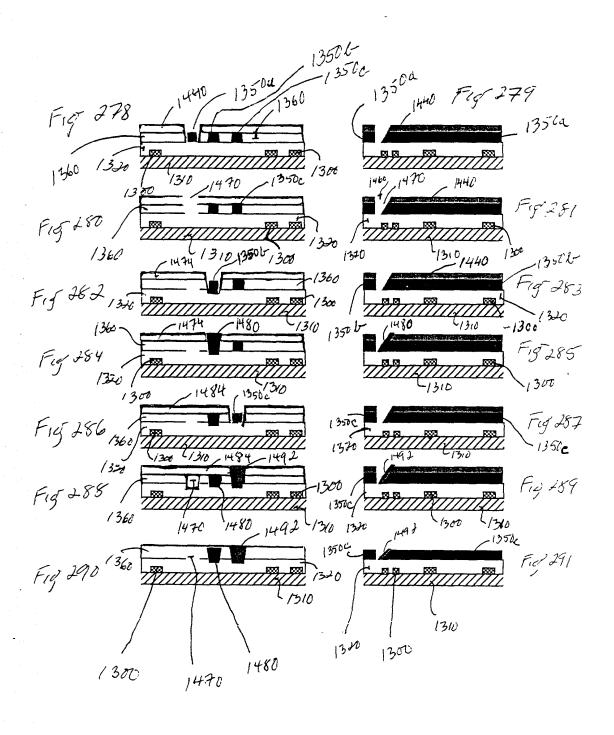


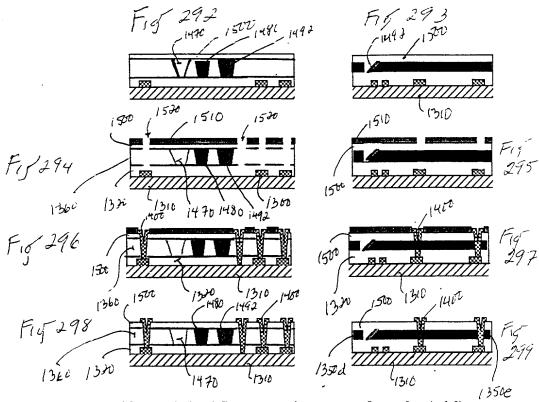




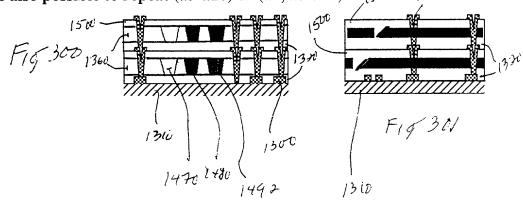


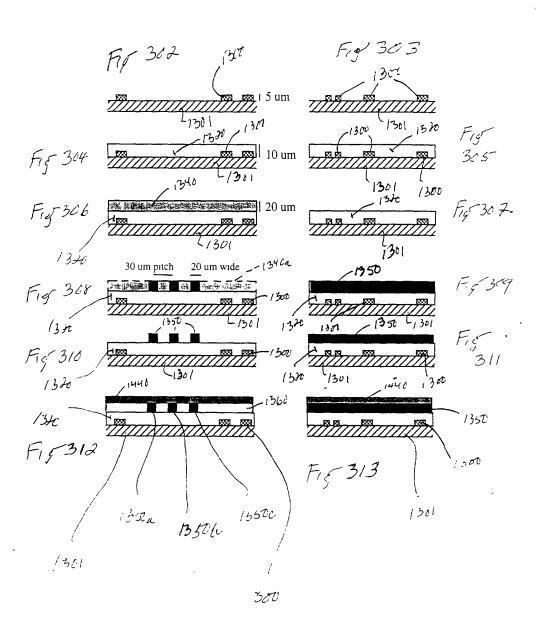


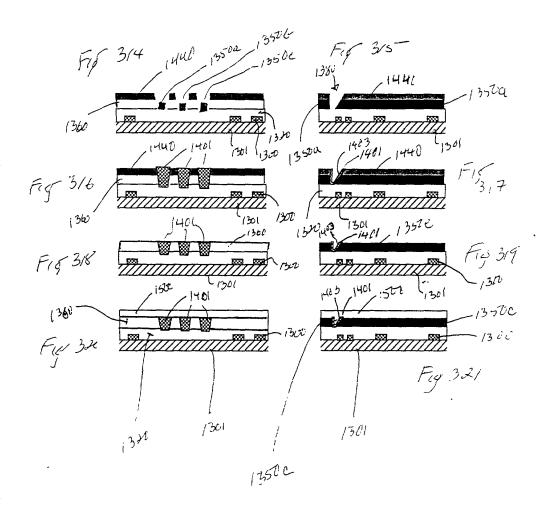


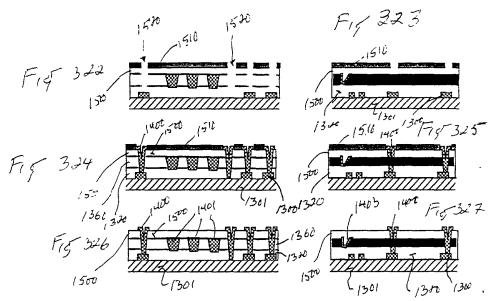


In the case of multi layer (a1-a16) process is repeated on the (a16). -it is also possible to repeat (a3-a16) or (a1, a3-a16)

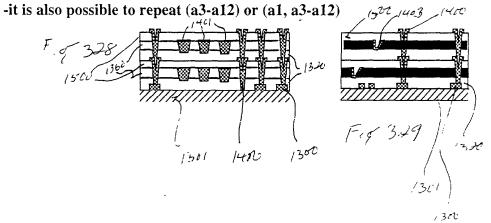


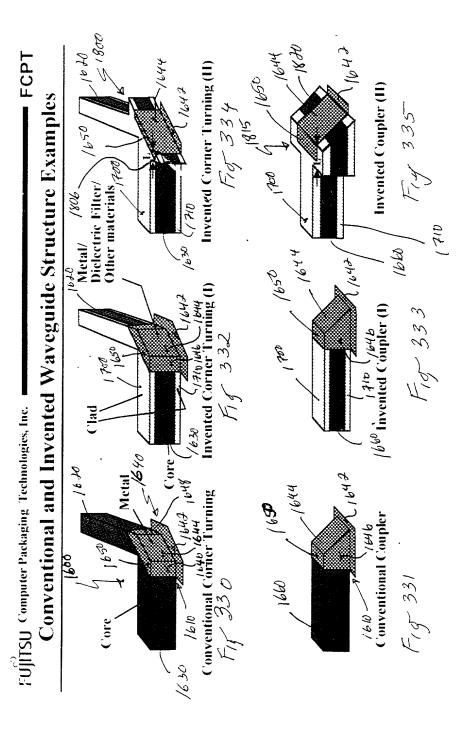


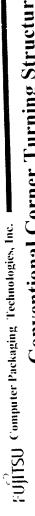


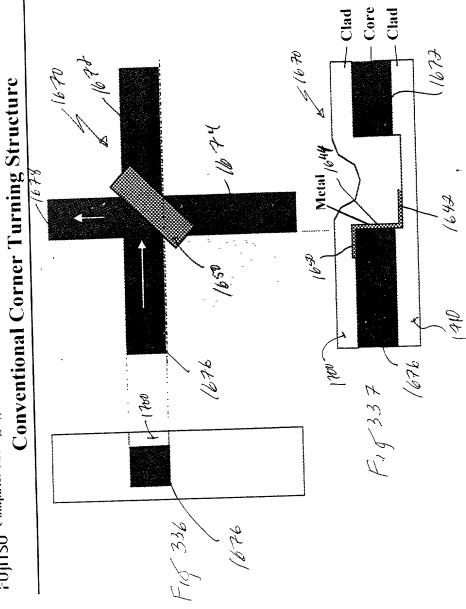


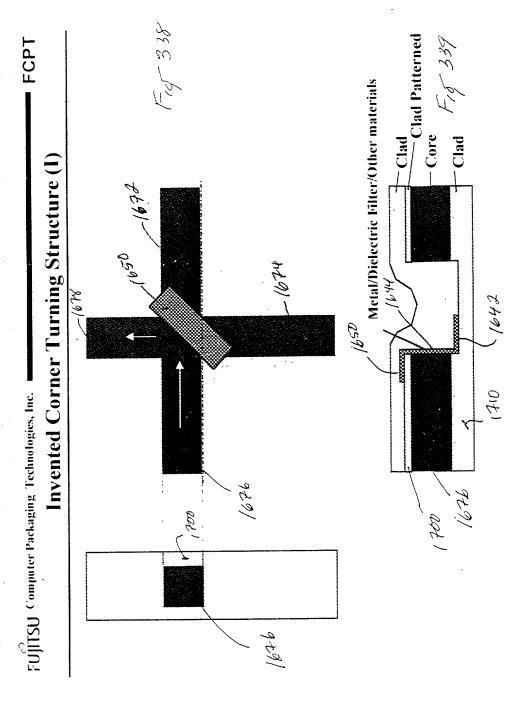
In the case of multi layer (a1-a12) process is repeated on the (a12).



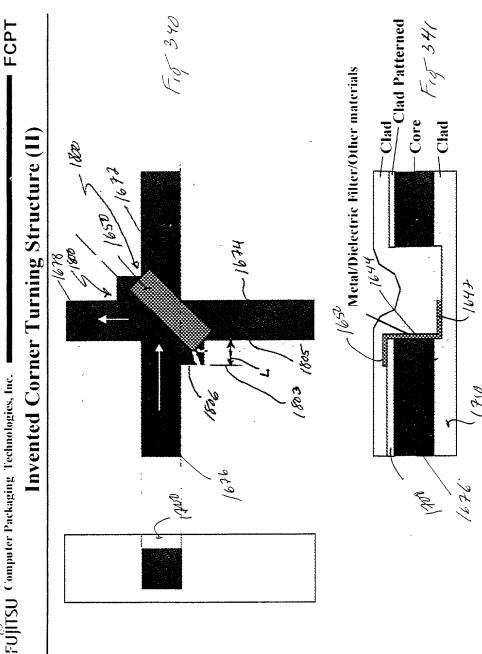




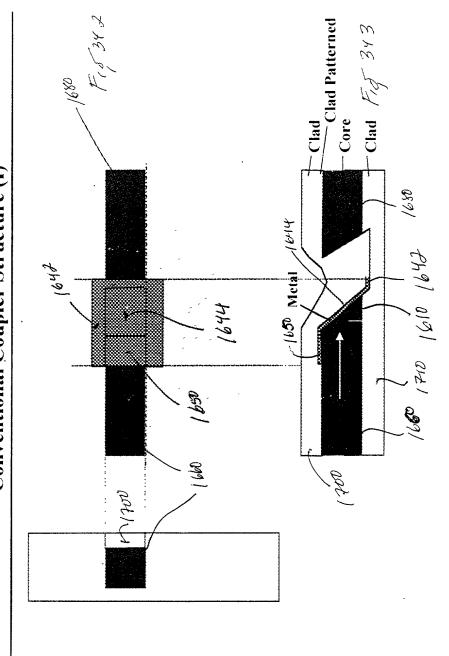


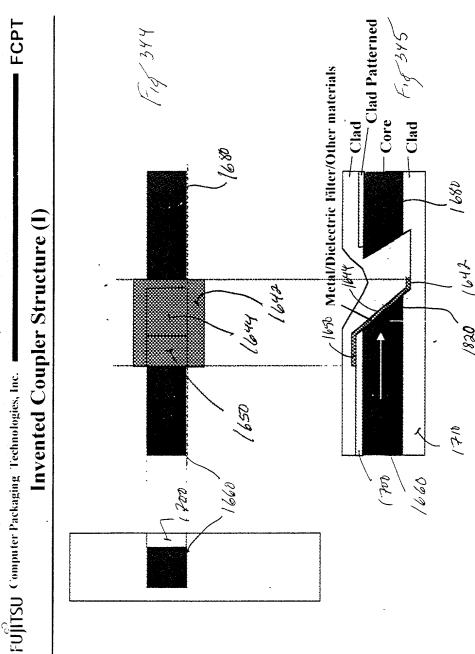


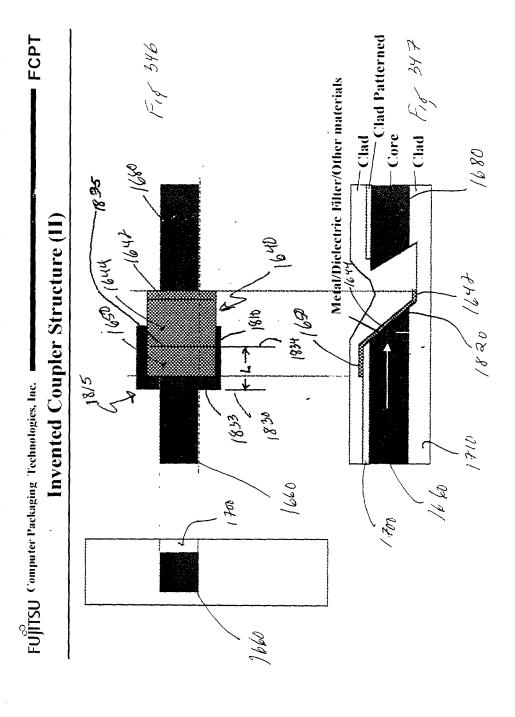
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Excimer Laser Ablation Example for Beveled Cut (2)

Beam Splitter

11, 12, 13, 14, 15, 16

11, 12, 13, 14, 15, 16

11, 19, 19

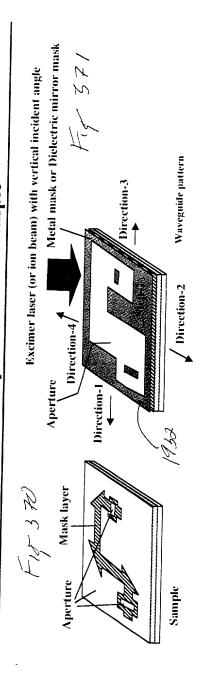
WDM DEMAX

Z-Connection Substrate Removal **FCPT** Aperture 179 367 (Fig. 366 Coupler Formation II AINA OF MINE FOF SO (19363 AINA OF MINE 179 Top Another Process Flow for Structure (II) 1436 F1954 Metallization Coupler Formation 1 Fig 360 Fg 3576 (MNA: Moving Neon Ablation) (MINE: Moving Neon Etching) F4357 至 FUJTSU Computer Packaging Technologies, Inc. 💻 19 358 Clad MINA OF MINE 355 Buffer/Clad/Core/Clad Waveguide Formation Shadow mask Mask Removal/
Metal or
Dielectric Filteror
Other materials Depo Fig 354 For Waveguide/Coupler Substrate Fig 351 Mask Mask formation 258, 67 1710) 1 te Red

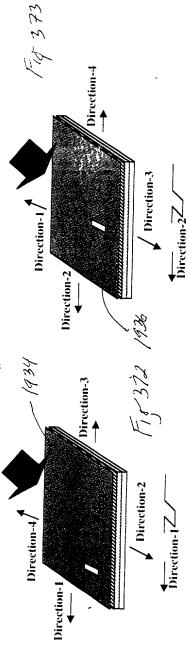
CUITSU Computer Packaging Technologies, Inc.

MNA, MNE Example for Add2 example

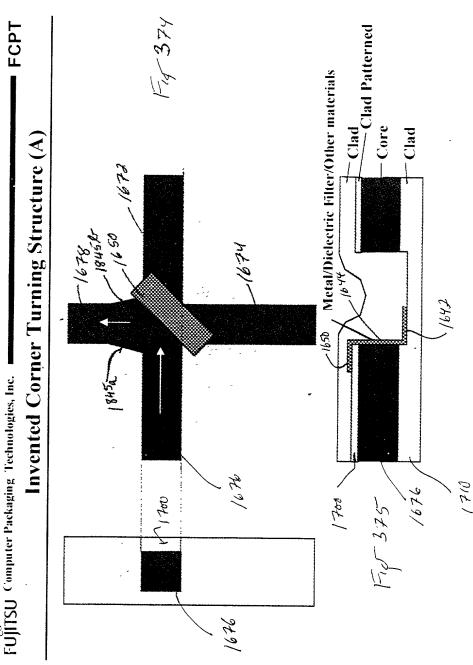
FCPT



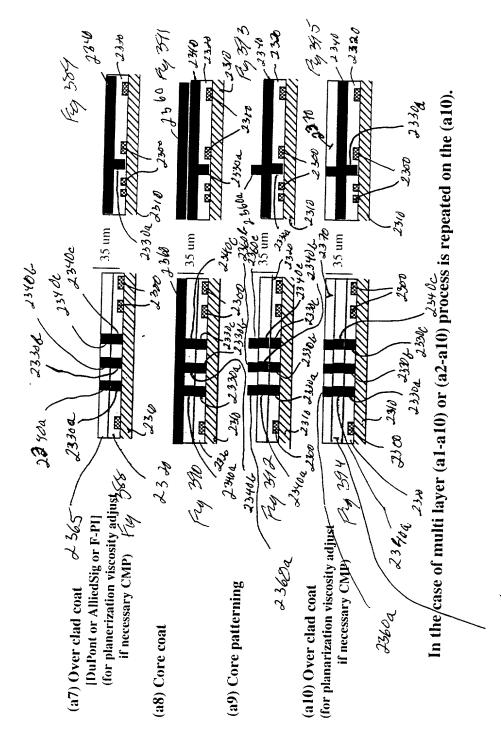
Excimer laser (or ion beam) with tilted incident angle



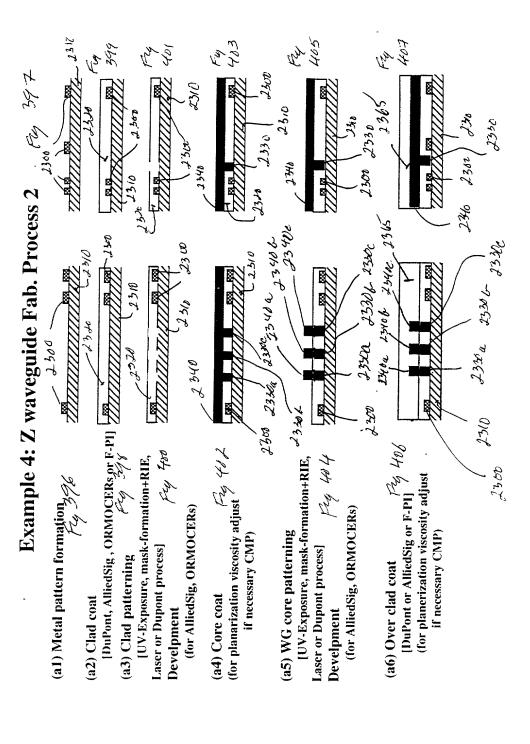
FUJTSU Computer Packaging Technologies, Inc.

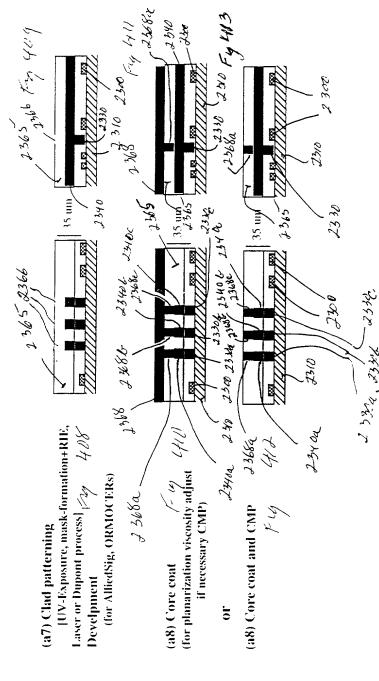


052 x 38 24.20 240 Example 3: Z waveguide Fab. Process 5 mm 3326 7226 233Ca hy 380 2330a |DuPont, AlliedSig., ORMOCERs or F-Pt] 222 Ex 378 Fry 382 (a1) Metal pattern formation $F_{u_{\!\!\!\! g}}$ 37 ℓ [DuPont, AllicdSig, ORMOCERs or F-P1] 23.40 [UV-Exposure, mask-formation+RIE, (UV-Exposure, mask-formation+RIE, (for AlliedSig, ORMOCERs) (for planarization viscosity adjust (for AlliedSig, ORMOCERs) (a3) Z-WG core patterning (a6) WG core patterning if necessary CMP) Laser, or Dupont process] Laser, or Dupont process] (a2) Core coaf9 (a4) Clad coat (a5) Core coat Develpment Develpment

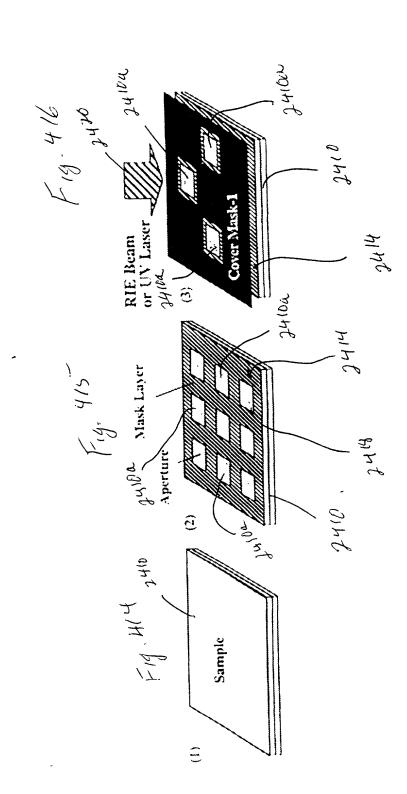


5967





In the case of multi layer (a1, a5-a8) or (a5-a8) process is repeated on the (a8).



420



. $$250\,\mu m$$ (b) Trench wall formation of three different angles

